

Design Challenges In Multi-GHz PLL Frequency Synthesizers

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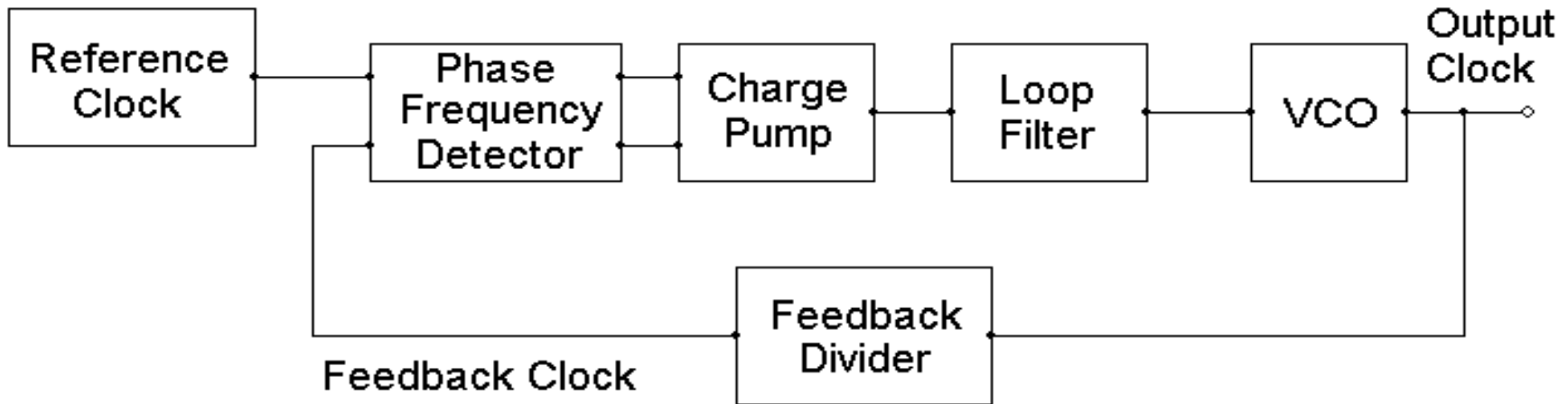
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OUTLINE

- PLL basics
- PLL second order effects
- PLL building blocks
 - Reference crystal oscillators
 - Reference path squaring buffers
 - Phase-frequency detectors
 - Charge-pumps
 - Loop filters (continuous and sampled)
 - Oscillators (LC and ring)
 - Output clock buffers
 - Dividers

What is a Phase-Locked-Loop?



- A **feedback system** that **aligns the clock edges** of a local controlled oscillator with the edges of a high stability input reference oscillator
- A low jitter output clock is obtained by using a large jitter local oscillator and a low jitter XTAL
- If a divider is present in the feedback loop, **frequency multiplication** is achieved ($f_{\text{out}} = N * f_{\text{ref}}$)

How a PLL Works ?

- A **phase detector** determines the phase difference between the **reference clock** and the **feedback clock** and generates a control signal that is smoothed by the loop filter
- The control voltage/current moves the oscillator frequency in the direction of eliminating the phase difference between the reference and output clock
 - If reference clock edges **lead** the feedback clock edges
→ oscillator frequency is **increased**
 - If reference clock edges **lag** the feedback clock edges
→ oscillator frequency is **decreased**
- **Phase alignment** is achieved by means of **frequency variation**

Type I versus Type II PLLs

- **Type I PLLs have a single pole at origin** ($s=0$ given by the intrinsic integration in the oscillator)
 - ↓ **finite phase difference** between reference and feedback clocks
 - ↑ potential **faster locking** (higher loop bandwidth)
- **Type II PLLs have two poles at origin** (one from the VCO and a second one from the loop filter/charge-pump)
 - ↑ **zero phase difference** between reference and feedback clocks

Process Independent PLLs

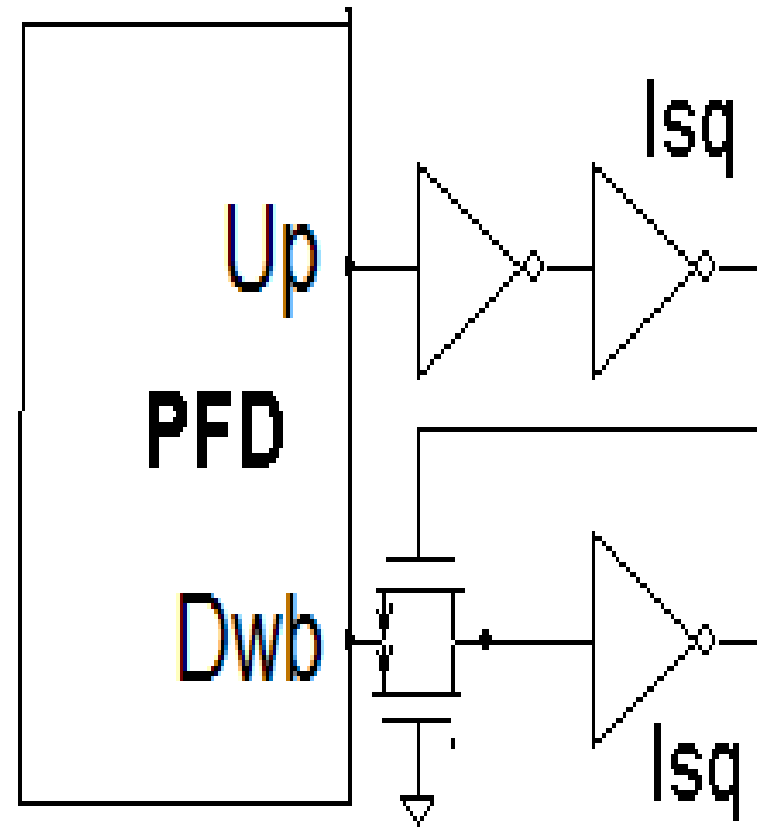
- **GOAL:** minimize or eliminate the process and temperature variation of the loop damping factor and/or bandwidth
- **Bandgap referenced:** set the charge-pump current equal to the ratio between a stable V_{bg} bandgap voltage and the on-chip resistor, $\rightarrow \xi = \text{const}$
- **Self-biased:** use as charge-pump current a fraction of the current that controls the oscillator (applicable to ICO only) such that ξ becomes proportional with a ratio of capacitors
- **Calibration:** measure the PLL open loop gain (for example by applying two constant phase differences and determine the output frequency) while the integral loop is hold constant and set the charge-pump current with a current-DAC to compensate the process variation of the loop gain (natural frequency)

Up/Down Charge-pump Current Mismatch

- Current mirrors have a finite current error due to:
 - V_T mismatch
 - Finite output impedance
- The PLL loop moves the edges of the feedback clock such that no net charge is injected in the loop filter over one clock cycle
 - Finite phase shift between reference and feedback clock edges \rightarrow loop filter voltage has a ripple that degrades PLL reference spurs

Up/Down Propagation Times Mismatch

- The finite propagation time through the output PFD inverter gives also a loop filter voltage ripple that degrades PLL reference spurs
- **Solution:** add a T_{gate} that is always ON in the output path that has one less inverter to match the propagation time of the inverter from the complementary path



Loop Filter Leakage Current

- A leakage current at the loop filter high impedance node **discharges** the integration capacitance
 - **Reverse current** of drain/source diffusion diodes
 - **Gate leakage** in deep submicron CMOS FETs
- Need to compensate the leakage current by **injecting a net charge-pump current** every reference clock cycle
- The current injected by the CP result in a **VCO control voltage ripple** which degrades PLL reference spurs

CP-PFD Transfer Function Dead-Zone

- If the charge-pump has a **large switching time**, it **cannot react** to small pulse width PFD control signals
- The absence of an answer from CP (a **Dead-Zone** in the PFD-CP transfer function) → the **PLL loop is opened** and the VCO clock edges can move unrestricted till the point where the CP will start reacting
- This phenomena results in a clock **jitter window** equal to the dead-zone
- **Solution:** introduce every clock cycle a period of time when **both Up and Down are active** such that the charge-pump **current legs turn-on** before they start measuring the phase difference between reference and feedback clock edges

CP Charge Injection and Clock Feed-through

- Each time the up and down CP switches turn-off, their **channel charge is injected** into the loop filter determining a VCO control voltage ripple → degrades reference spurs
- **Solution:** Avoid the switch charge injection by adding dummy switches that **capture** the charge released by the turning-off switch and **release** the charge required to create the channel in the turning-on switch
- Finite C_{gd} capacitances of the FET switches determine the **clock feed-through** from the PFD control lines to the loop filter voltage, resulting in a ripple on the oscillator control signal → degrades reference spurs
- **Solutions:**
 - reduce the size of the switches → decrease C_{gd}
 - Use a smaller control voltage swing

Charge Sharing between CP nodes

- Finite capacitances exist at the drains of the Up/Down CP current mirrors
- When the CP switches turn-off the Up/Down currents discharge these nodes to the corresponding supply line (V_{dd}/V_{ss})
- When the CP switches turn-on again, these parasitic capacitances need to be charged to the loop filter control voltage (V_{ctrl})
- Depending on the V_{ctrl} voltage level a net charge need to come from the loop filter capacitor to charge the parasitic capacitances → generates a V_{ctrl} ripple which degrades PLL reference spurs
- **Solution:** Use a bootstrap buffer which keeps the potential at the drains of the current sources equal to V_{ctrl} when the CP switches are OFF

Delay in the PLL Feedback Loop

- All digital circuits have a **finite delay time** (inverter buffers, PFD, Feedback Divider)
- A delay block $\exp(-s \cdot T_d)$ introduces a linear varying phase shift as a function of frequency $\varphi = -\omega \cdot T_d$
- This phase lag degrades PLL's phase margin by $\Delta\varphi = \omega_C \cdot T_d$
- Feedback loop delay is particularly troublesome in **large bandwidth PLLs** (e.g. fast locking ring oscillator PLLs) where $\Delta\varphi = \omega_C \cdot T_d$ can assume large values
- A degraded phase margin leads to:
 - More **peaking in the transient locking waveform** which can stress in frequency the divider if it has a small margin from its maximum operating frequency
 - **Peaking in the jitter input-output transfer function** which degrades the output clock phase noise performance

PLL Sampling Effect

- The phase comparison is not done continuously, but in a discrete time manner → **PFD compares the phases** of the reference and feedback clock only based on their edge position which lead to a **sampled data system**
- After the phase comparison is done, no other action is taken till the next reference clock cycle → this is equivalent with a hold operation applied to the phase difference measurement
- The transfer function of a **zero-order hold** sampled data system is $(1-\exp(-s*T))/s*T$
- This intrinsic PLL phase sample and hold operation introduces a **phase lag** in the feedback loop which degrades the PLL phase margin → jitter peaking
- $\varphi = -\omega * T_{/2} \rightarrow \Delta\varphi = \omega_C * T_d / 2$

Divider Failure During Transient Locking

- In many multi-GHz PLLs the feedback divider **operates close to the maximum frequency** allowed by the CMOS process, which leaves very little margin for **peaking during the transient locking** process
- There are two **main causes** for transient peaking
 - **Poor loop damping** (small signal behavior) → use a process independent damping factor architecture which keeps $\xi > 1$
 - **Large phase difference between reference and feedback clock** at the point when the frequency locking is achieved and the phase locking starts → this peaking can be very large in **wide-bandwidth PLLs** where the oscillator control voltage can vary with a large Δ even in a single reference clock cycle
- If during the transient locking the maximum operating frequency of the divider is exceeded and it fails to provide an output edge → **PLL fails to lock and fails to recover**

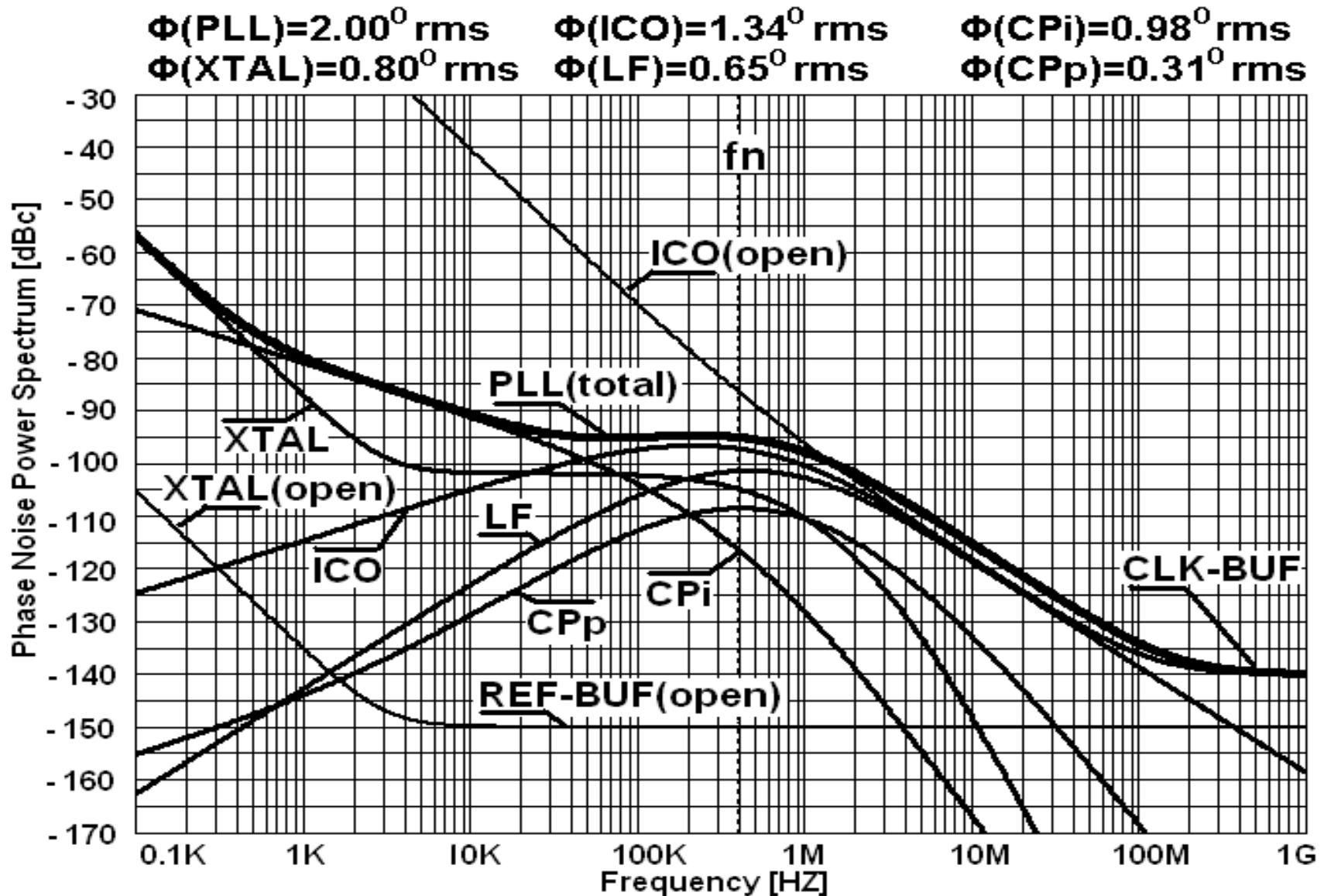
Divider Failure During Transient Locking - Continued

- **Solution 1** (for small signal peaking)
 - The peaking of a linear system is proportional with the input signal step (frequency change)
 - To minimize the transient locking peaking at frequency change in the synthesizer the output **frequency range is divided in several sub-ranges** and thus the single large step locking process is replaced with several smaller frequency steps locking processes, leading to a much lower peaking amplitude
- **Solution 2** (for nonlinear peaking)
 - Add a circuit in the PFD that **limits the maximum Up control signals pulse width** to a fraction of the reference clock period (e.g. $T_{ref}/4$ or $T_{ref}/8$) – undershoot during transient locking is not an issue
 - Limiting the maximum pump-up time period reduces the nonlinear peaking amplitude
 - Restricting the pump-up period **increases the frequency locking process** – can become an issue in fast frequency switching PLLs

PLL Phase Noise Analysis

- **Reference clock** path (XTAL, REF-BUF) phase noise is **low-pass filtered** by the PLL → low phase noise output clock asks for a low loop bandwidth
- **Charge-pump** noise is also **low-pass filtered** as all the front-end noise components
- **Controlled oscillator** phase noise is **high-pass filtered** by the PLL → high phase noise oscillators (ring oscillators) require a low loop bandwidth
- **Loop filter** noise is **band-pass filtered** by the PLL
- All corner frequencies of the low-pass/high-pass/band-pass transfer functions are equal to the **loop natural frequency**
- **LC** oscillator based PLLs use **low loop bandwidths** → does not have demanding requirements for reference path noise
- **Ring** oscillator based PLLs use **high loop bandwidths** to adequately reject VCO's large phase noise → need a low phase noise reference path

Example of PLL Output Phase Noise



PLL Output Clock Spurs

- **DIRECT INJECTION SPURS**

- **Reference spurs** → generated by a finite ripple on the oscillator control signal at the reference clock frequency →
 $f_{\text{spur}} = f_{\text{out}} \pm f_{\text{ref}}$

- **Supply injected spurs** → determined by a finite PSRR of the PLL blocks → $f_{\text{spur}} = f_{\text{out}} \pm f_{\text{perturb}}$

- **MIXING SPURS**

- Nonlinear operations such as **clock edge squaring** and **charge-pump chopping action** are capable of creating intermodulation frequencies $f_{\text{spur}} = k \cdot f_{\text{ref}} \pm p \cdot f_{\text{perturb}}$
- If the intermodulation spurs fall in the PLL bandwidth where minimal rejection exists → large output spurs can be generated → need high PSRR regulators
- The spurs in the REF-BUF are amplified by the PLL gain (N)

Crystal Oscillators Requirements

- Keep the **amplitude constant** with process and temperature → need to use an Automatic Amplitude Control loop (**AAC**)
- **Maximizing the oscillating amplitude** (without crashing the active devices) → minimizes the oscillator **phase noise**
- Reducing **thermal noise** in amplifier and AAC loop decreases the **1/f² phase noise** while reducing **1/f noise** in amplifier and AAC loop decreases the **1/f³ phase noise**
- **Minimize the resistive and capacitive loading** on the crystal → keeps a high loaded Q of the tank → improves 1/f² phase noise performance
- Ensure a **safe oscillator start-up** requires a positive loop gain higher than 1 over all design corners. Optimum value from phase noise perspective is 2 → keep the loop gain 1.5-3 over process and temperature corners

XTAL Oscillators Configurations

- **Common-source amplifier (Pierce Oscillator)**
 - ↑ does not need floating capacitors → all capacitors can be MOS
 - ↓ need two pins to connect the crystal
 - ↓ use both NFETs and PFETs → increased $1/f^3$ phase noise
 - ↓ bias network loads the crystal → degraded loaded Q
 - ↓ need a linear buffer if the sinusoidal clock need to be driven off-chip
- **Common-drain Amplifier (Colpitts Oscillator)**
 - ↑ need a single pin to connect the crystal
 - ↑ does not need a linear clock buffer to drive the sine-clock off-chip
 - ↑ can use only PFETs → minimize $1/f^3$ phase noise
 - ↑ show lower loading on the crystal tank → higher Q → minimize $1/f^2$ phase noise
 - ↓ need a floating capacitor (MIM or Metal Cap. which takes a large die area) → cannot be implemented with MOS capacitors due to their large substrate noise injection

XTAL Oscillators Configurations - Continued

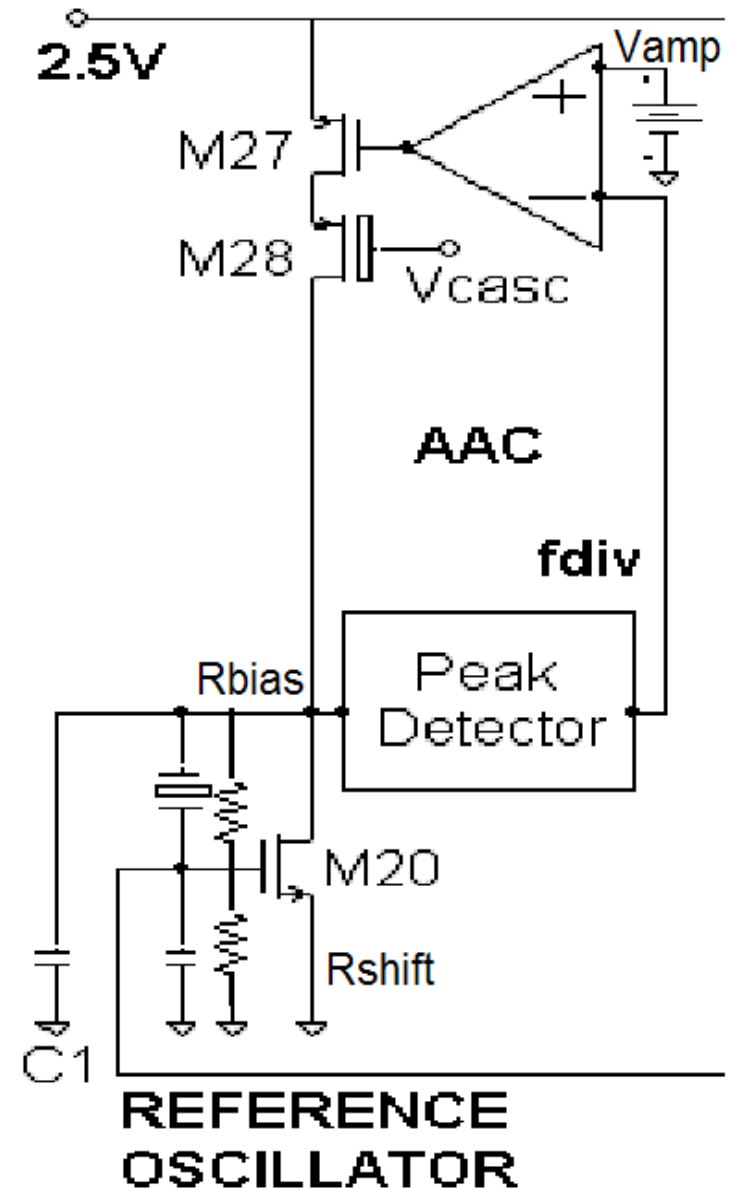
- **Common-gate** amplifier (also Colpitts Oscillator)
 - ↑ need a single pin to connect the crystal
 - ↑ can use only PFETs → minimize $1/f^3$ phase noise
 - ↓ need a floating capacitor (MIM or Metal Cap. → large die area)
 - ↓ difficulties to bias the amplifier as both the drain and source need to see large impedances → headroom voltage issue
- Pierce oscillator → widely used for their area efficiency
- Colpitts oscillators → preferred in low phase noise applications → require larger die area

Pierce Crystal Oscillator

- **Two solutions** for the amplifier
 - NFET amplifier → requires a PFET AAC mirror
 - PFET amplifier → requires an NFET AAC mirror
- To minimize phase noise the **amplifier need to be operated in class C** → inject noise only at the peak amplitude points where the impulse sensitivity is at its minimum
- AAC loop is ON all the time → prefer to use PFET amplifiers due to their lower $1/f$ noise
- **Conclusion:** NFET amplifier in class C and PFET AAC loop is the best Pierce oscillator architecture

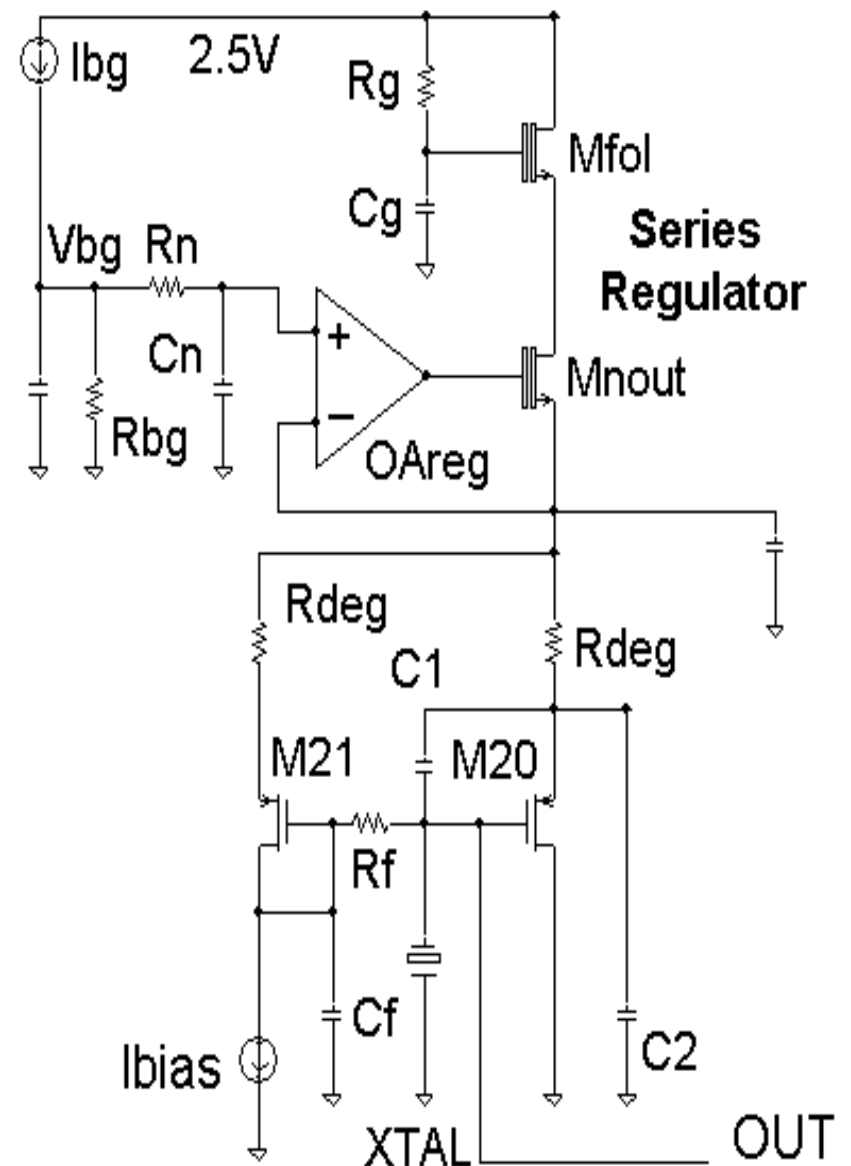
NFET Amplifier Pierce Oscillator

- Use **thin oxide devices** to reduce the $1/f^3$ phase noise (thick oxide devices have larger $1/f$ noise at same device area)
- **Amplitude decreases** (lower **breakdown voltage**) → decrease S/N
- **Rbias** ensures a diode DC connection → need to be large to avoid loading the crystal
- **Rshift** shifts-up the DC voltage in the drain of the amplifier → achieves a larger amplitude → lower phase noise
- Avoid crushing the amplifier → reduce the $1/f^2$ phase noise



PFET Common-drain Oscillator

- Use PFET amplifier and PFET AAC to minimize $1/f^3$ p. noise
- Using a current load in the source of the amplifier prevents the class C operation \rightarrow need to use a current mirror architecture
- M20,M21 mirror provides the DC bias current
- Class C operation of the amplifier \rightarrow inject noise only at minimum impulse sensitivity
- Need a floating capacitor C1 that takes large area (MIM)

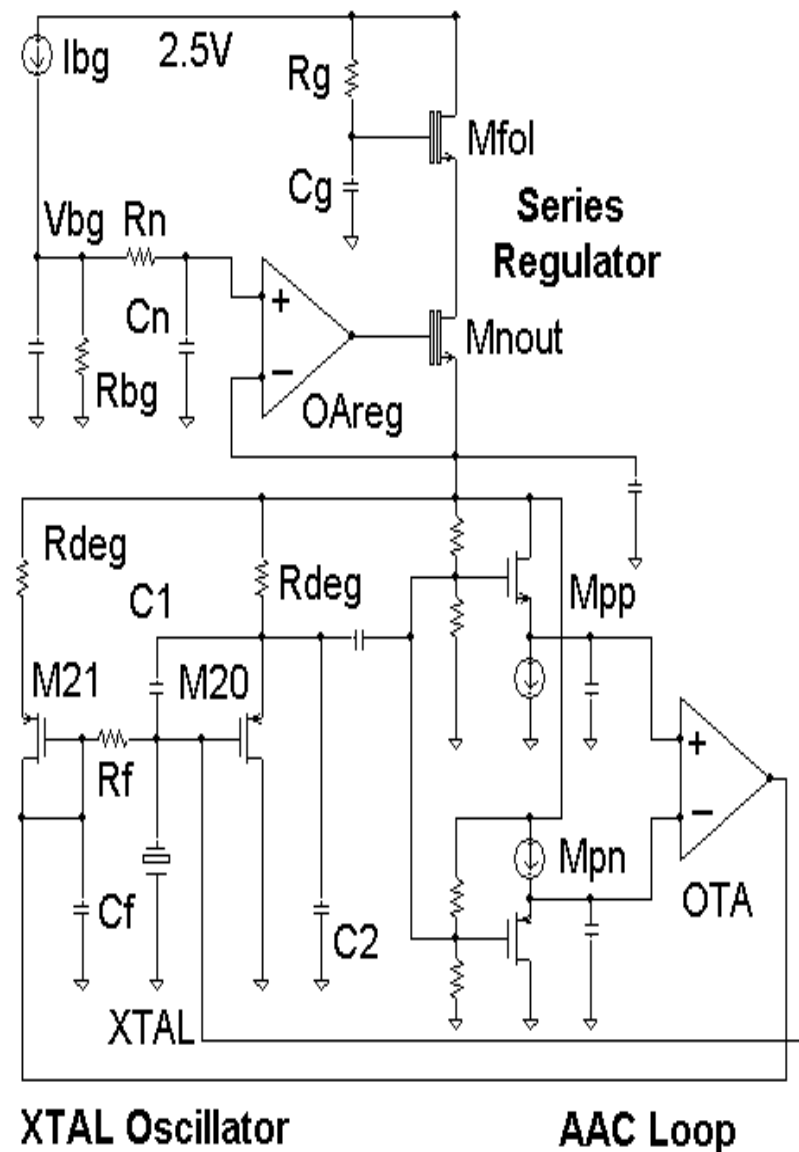


Automatic Amplitude Control Loop

- The **AAC noise** generally **dominates the phase noise** of a well designed XTAL oscillator → it is always ON and injects noise also around clock edges
- Without AAC the amplitude of oscillation can vary over a wide range (e.g. 2x) with process and temperature → degrade significantly the phase noise in the worst case corner
- Three available types of AAC:
 - **Continuous time AAC** → adjust continuously the bias current of the amplifier based on the measured peak amplitude → add noise during the entire clock cycle
 - **Hybrid continuous-discrete AAC** → perform the amplitude correction only at discrete time intervals but still use an AAC loop amplifier
 - **Discrete AAC** → replace AAC amplifier with a digital state machine that takes the decision for the loop drive direction

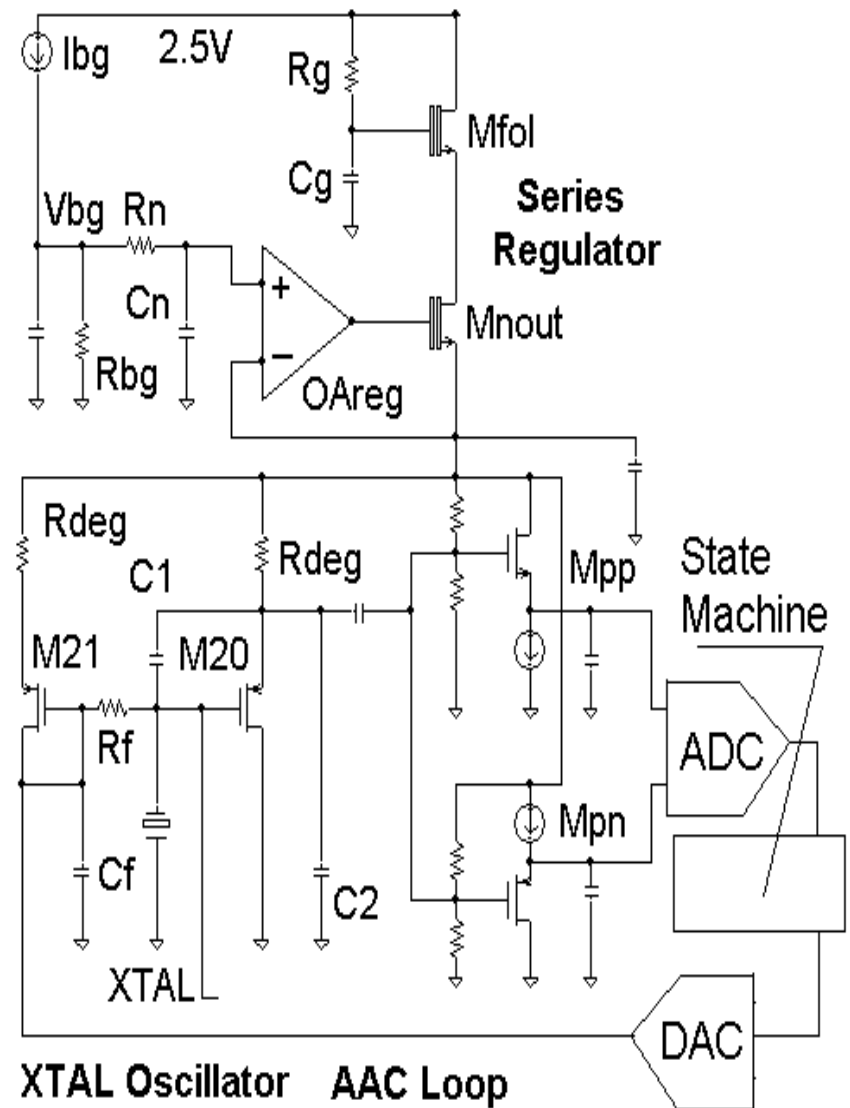
Continuous Time AAC Loops

- Use positive and negative peak detectors to measure the peak-to-peak amplitude
- Prefer AC coupling of peak detectors → separate bias points
- OTA sets the bias current of the amplifier such that the measured amplitude equals the reference voltage ($V_{Tp} + V_{Tn}$)
- PFET OTA and PFET bias mirror → minimize $1/f^3$ p. noise
- Use large resistive degeneration to reduce the thermal noise of the bias mirror
- $PN \approx -125\text{dBc/Hz @1KHz}$



Discrete Time AAC Loops

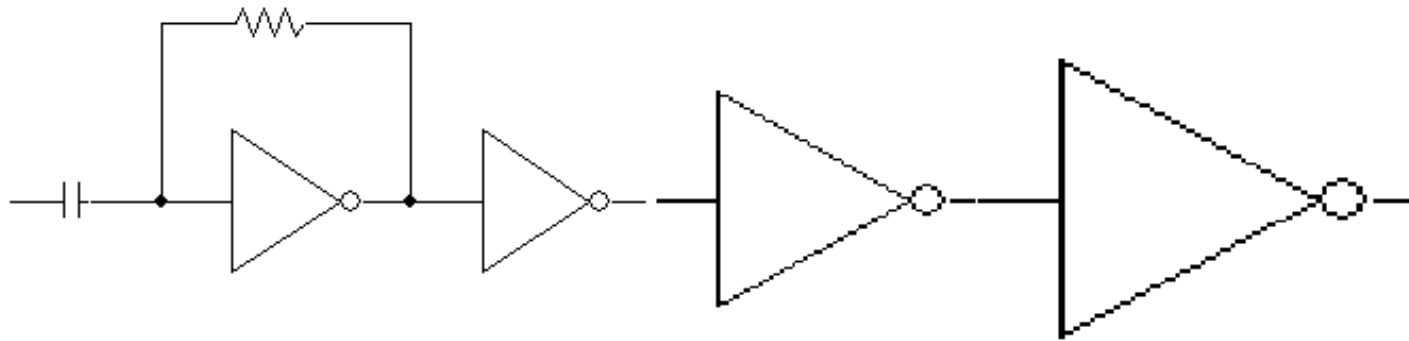
- AAC amplifier is the dominant noise contributor → **replace it with a digital state machine** which takes the decision for driving the AAC loop
- Need an **ADC** to convert the measured peak amplitude into a digital control word for the state machine
- Need a **DAC** to convert back to current (analog) the state machine output
- Both ADC and DAC need only moderate resolutions (6-8 bit)
- $PN \approx -145\text{dBc/Hz @1KHz}$



Reference Clock Squaring Buffer

- Square-up the sinusoidal clock from the crystal oscillator with minimal added noise
- Present a rather constant input impedance to the crystal oscillator → do not impact its phase noise
- **First buffer stage** generally dominates the noise of the squaring buffer → need high gain to speed-up the clock edges → second stage need to present a low capacitive load to the first stage
- Spurs present on the supply line are down-converted around the reference clock carrier → need a high PSRR regulator
- Noise on the supply line is up and down-converted around the carrier → need a low noise regulator

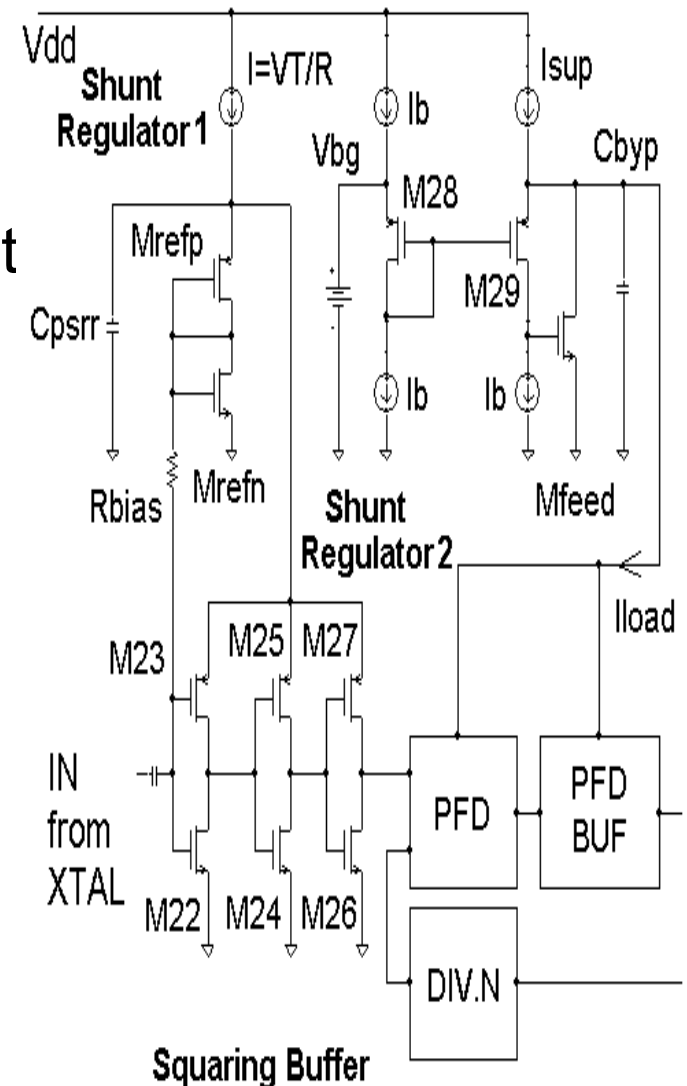
Reference Clock Squaring Buffer



- **AC coupled** to avoid pulse width distortion due to XTAL bias point variation with process and temperature
- First inverter need to have a **high gain, low thermal noise** and **low 1/f noise** → large device area and high W/L
- The **second buffer** need to be small to minimize load on the first stage → only large enough to just pass the fast edges created by the first stage
- Scale-up following buffers to ensure PFD driving requirements
- The number of inverters need to be selected such that PFD is driven by the XTAL **edge that has lower phase noise**

Current Starved Squaring Buffer

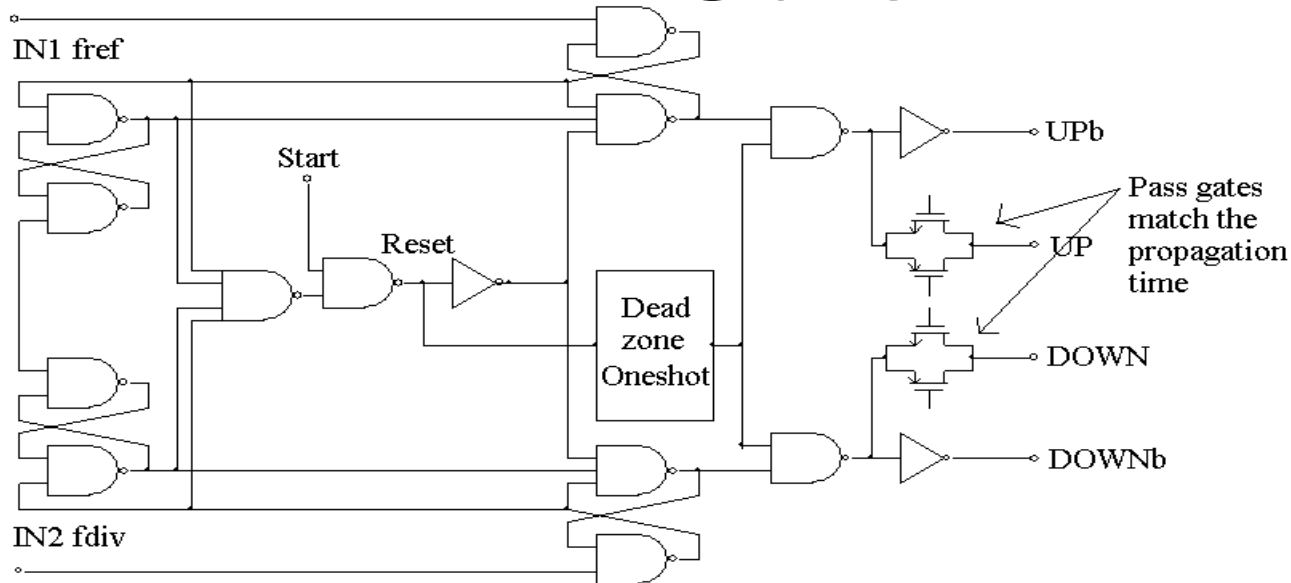
- Limit the current available to the inverter around the crossover point → minimize phase noise as only one of the two devices in the inverter is ON at a given time (use a $V_{Tp} + V_{Tn}$ supply)
- Rbias resistor that provides the DC bias to the first inverter shows a negligible load to the crystal oscillator
- slows-down slightly the edges but the gain from the reduced noise is larger
- Use an open loop shunt regulator to avoid reference spurs leakage to the global PLL supply
 - Low freq. PSRR limited by $r_{out}(I_{bias})/(2/g_m)$
 - High freq. PSRR limited by $C_{gd}(I_{bias})/C_f$



Phase Frequency Detector Requirements

- **Fast reset propagation** time to minimize the width of the up/down pulses in lock condition → improve reference spurs due to less CP mismatch current injected in the loop filter
- **Fast rise/fall times** to reduce the sensitivity to both gate intrinsic noise and supply noise → minimize PFD phase noise contribution
- **Matched propagation times** for up/upb/dw/dwb control signals → improve reference spurs
- **Matched slew-rates** for the four PFD output signals up/upb/dw/dwb
- Provide the voltage level shifting required by the CP

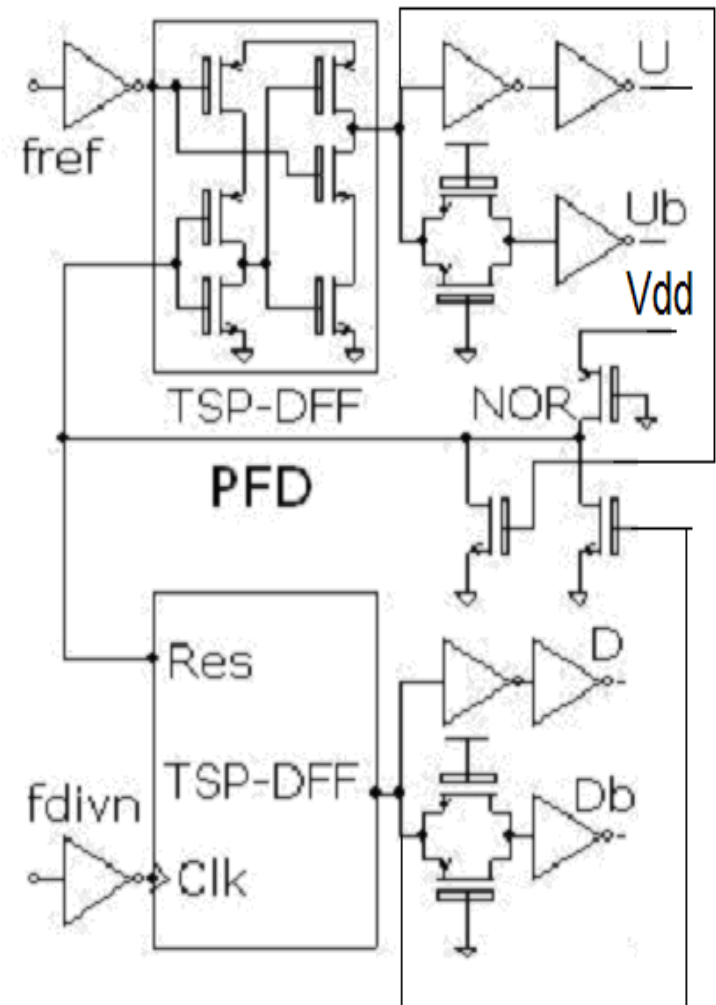
7 NAND Gate PFD



- The **faster input of the NAND gate** (the NFET closer to the output) need to be used for the reset propagation signal
- The up/dw pulse width in lock condition is equal with $7 \cdot T_{\text{delay}}$ of the NAND gate and is limited to 0.35-1ns \rightarrow reference spurs $< 50 \text{ dBc}$
- If the CP has a slow switching time, additional inverters can be added in the reset path such that the minimum up/dw pulse width is extended in excess of the T_{cp} switching time \rightarrow no dead zone in the CP-PFD transfer function

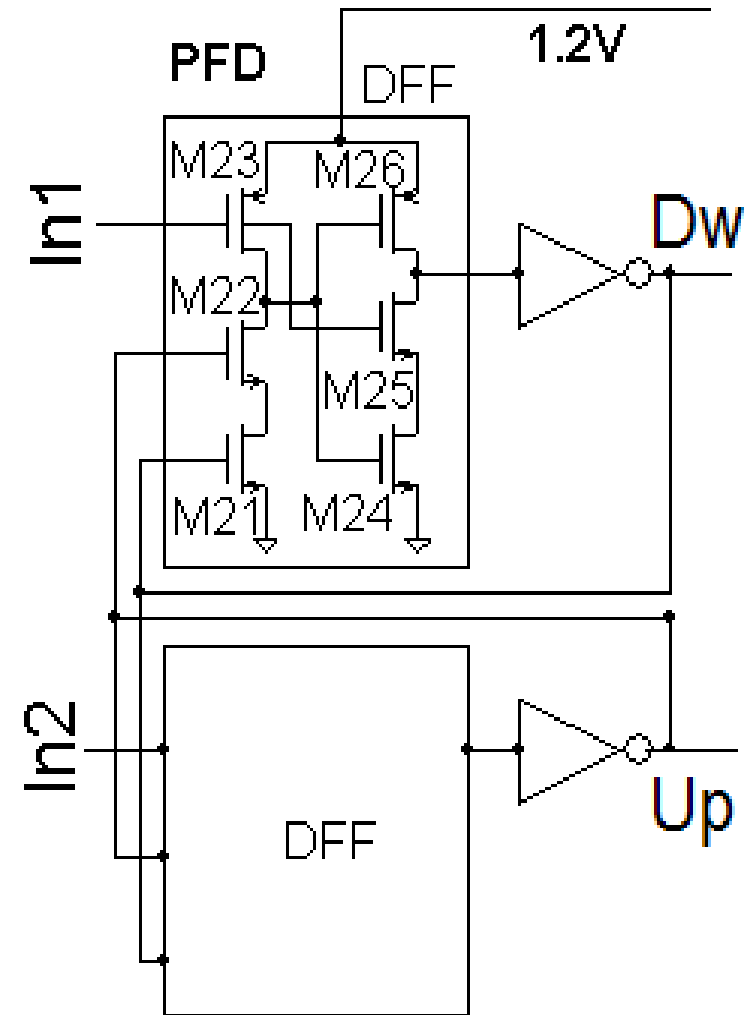
Dynamic D-Flip-Flop PFD

- To reduce the reset propagation time (which limits the up/dw pulse width) the PFD can be implemented with **dynamic** (pre-charged) DFFs
- The **NMOS NAND gate** used for the reset decoding is much faster than the standard CMOS gate, reducing the up/down pulse width → DC current
- DFF sensitive to the XTAL falling edge which has less phase noise (PFET is driving)



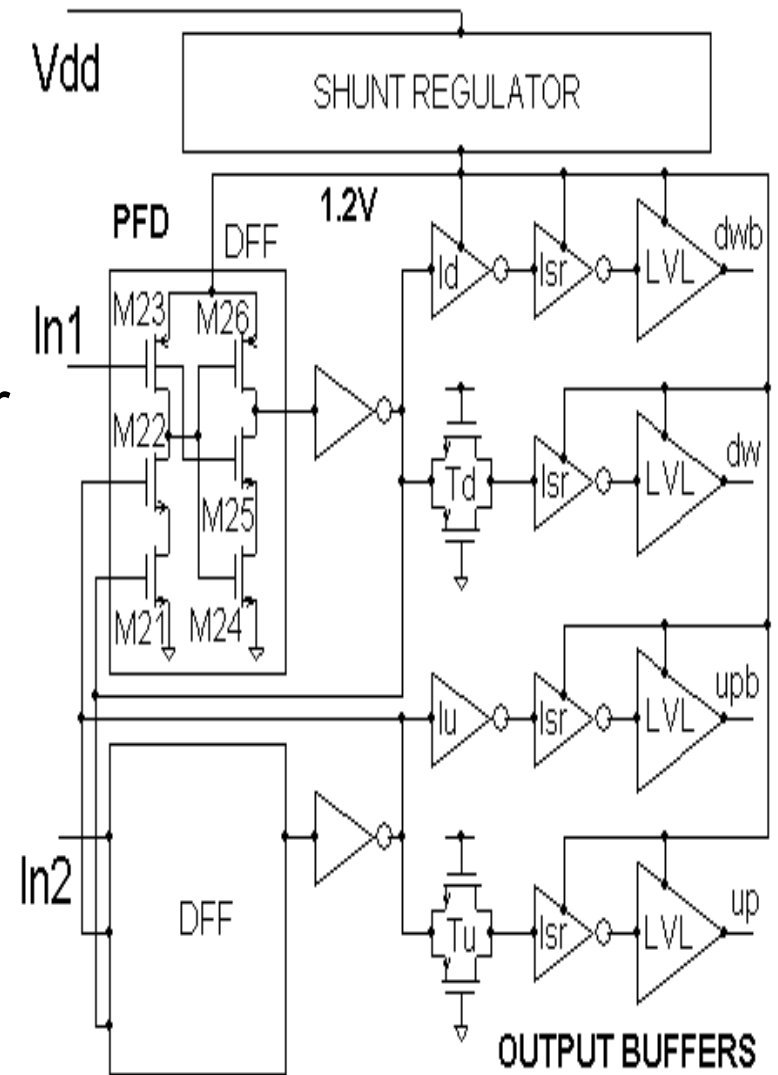
Dynamic DFF PFD with Embedded Reset NAND Gate

- To further reduce the reset propagation time the reset NAND gate was **built-in** the dynamic DFF
- The up/dw pulse width is reduced to $3 \cdot T_{\text{delay}} = 150\text{ps}$ → reference spurs decrease to $-60 \dots -65\text{dBc}$
- DFF sensitive to rising edge → need an additional inverter at each input in order to still use the lower phase noise edge



Balancing the Propagation Times and Slew-Rates of PFD Output

- The PFD provides only two outputs (up/dw), while the differential current steering CP requires also the upb/dwb complementary signals
- Upb/dwb obtained by adding a parallel path having one extra inverter
- Add **always-ON transmission gates** T_u/T_d to balance the extra inverter delay
- After t-gates the **edges are slower** in comparison with the inverter output
- Add two more layers of inverters to balance the slew rates of all 4 PFD outputs



PFD Level Shifters

- For fast propagation times the **PFD** need to use the **thin oxide devices** from a dual gate oxide CMOS process (e.g. 0.13 μm from a 0.13 μm CMOS) and a low supply voltage (1.3V)
- In contrast the **charge-pump** need to use **thick oxide devices** and higher supply voltage (0.35 μm from a 0.13 μm CMOS and 2.5-3.3V)
- A **level shifter** need to be introduced between the PFD and the CP to make the conversion between the two logic signals
 - Need to maintain fast edges
 - Minimize power consumption

Cross-Coupled Level Shifters

- Use a cross-coupled (positive feedback) latch configuration to regenerate the logic levels
- Standard way of building a level shifter
 - ↑ does not take DC bias current
 - ↓ cannot achieve very fast edge slew-rates due to the large gate capacitance load present at the two output signal nodes

Mirror-Protected Level Shifter

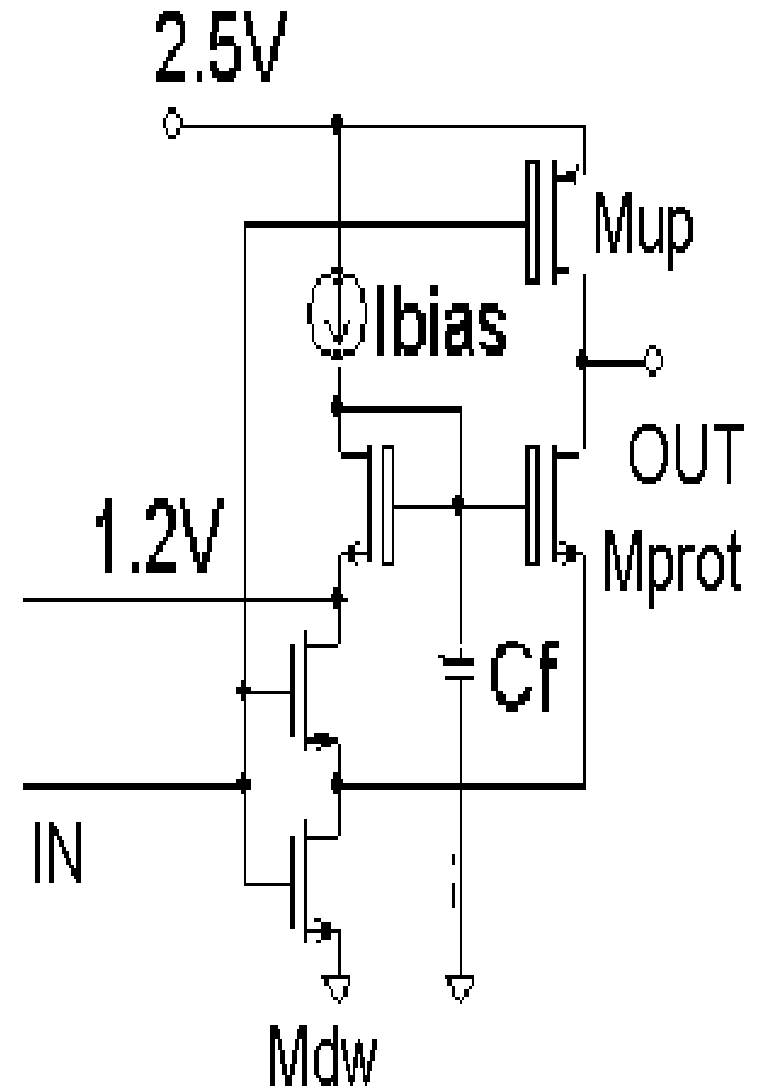
↑ does not use cross-coupled structures that load excessively the signal nodes
→ much **faster edge speed**

↓ need a DC bias current

- **pulling-down** is provided by the Mdw low voltage FET

- **pulling-up** is ensured by the Mup high voltage FET

- Mprot high voltage current mirror **protects** the Mdw FET when the output is High



Charge-Pump Requirements

- **Equal I_{up} and I_{down}** for all output voltage levels → reduce reference spurs
- High **output impedance** → reduce current mismatch and also improves PSRR
- **Equal up/down switching times** (combined with PFD outputs propagation times)
- **Low thermal and $1/f$ noise** → large area and low gm devices → need large headroom
- **Low clock feed-through** → dummy switches
- **Low supply and substrate coupled spurs**

Charge-Pump Architectures

- **Single ended CP**
 - ↑ lower loop filter capacitance
 - ↓ higher substrate/supply noise coupling
- **Differential-In Single-ended-out CP**
 - ↑ still does not need double loop filter capacitance
 - ↑ Faster switching (current steering)
 - ↑ less spur sensitivity
- **Differential-In Differential-Out CP**
 - ↑ best supply/substrate/clock feed-through performance
 - ↓ need double loop filter capacitance area
 - ↓ Need a common-mode feedback circuit that increases CP noise contribution

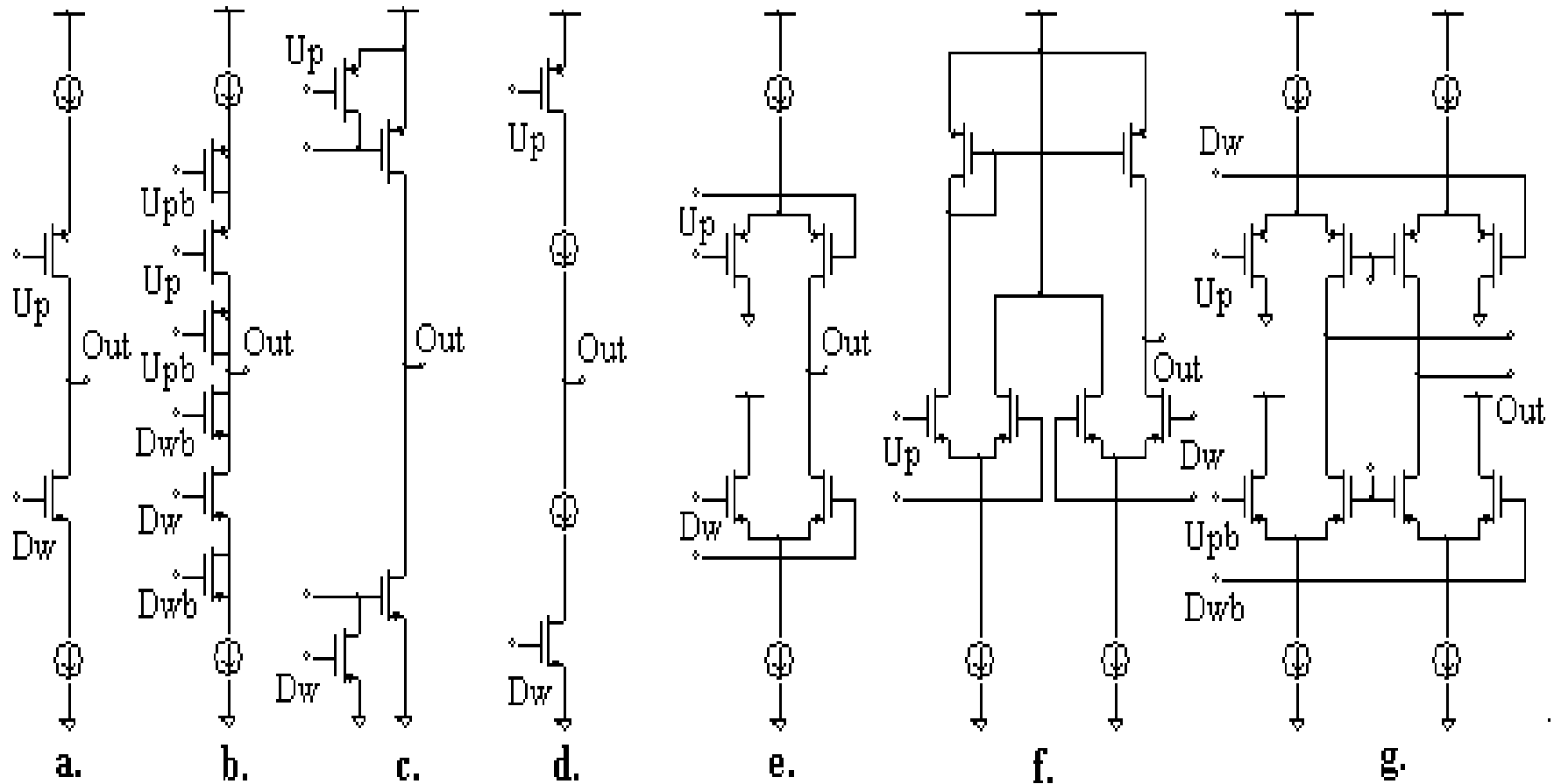
Charge-Pump Styles

- **All NMOS CP**
 - Use only the fast devices in the switching stages
 - Good matching of up/down current values and switching times
 - Need a turn around PMOS current mirror that adds a supplemental low frequency pole in the loop (also has a finite switching delay time)
- **Complementary NMOS/PMOS CP**
 - Need reasonable fast complementary devices
 - Have a large mismatch between I_{up} and I_{down} switching times → degrades reference spurs

Charge-Pump Configurations

- **Drain-switch**
 - **Large current spikes** at beginning of the turn-on when both the current mirror and the cascode switch are in triode region
 - **Large clock feed-through** (switch connected directly to the loop filter)
 - Relatively **long switching time**
- **Source-switch** (best single ended CP)
 - **Fast switching** (switch connected at a low impedance node)
 - **Less clock feed-through** (switch is not directly connected to the loop filter)
 - **Low switching spikes** (devices switch between OFF and On in saturation region)
- **Gate-switch** → slow – not used in single ended form

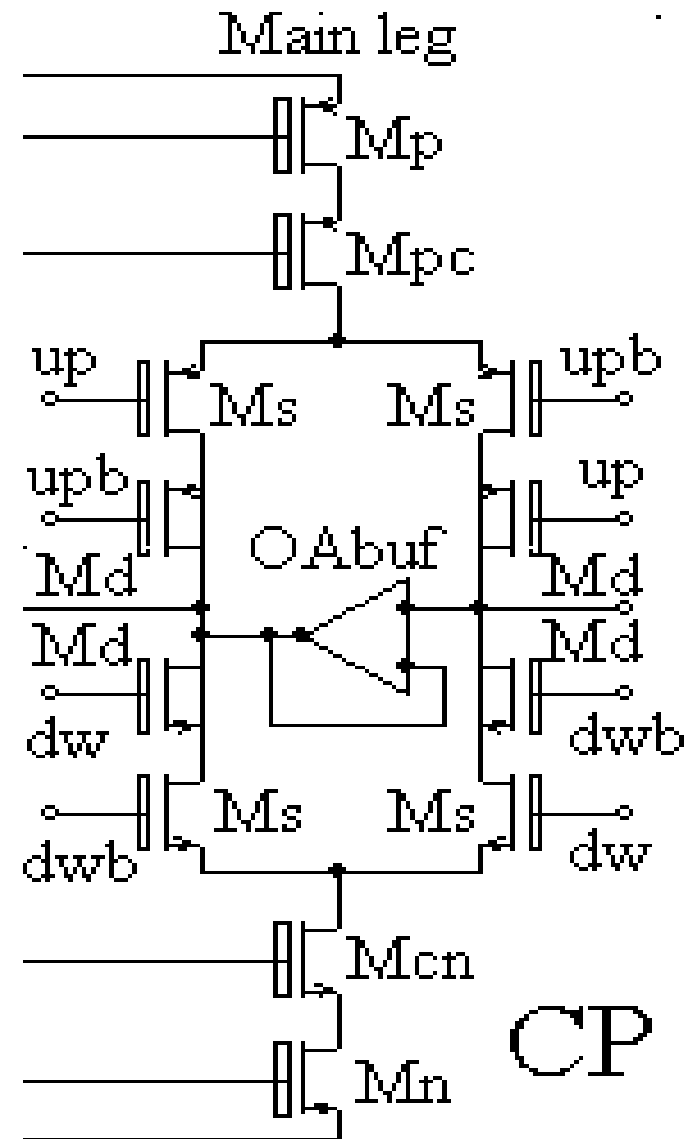
CHARGE-PUMP ARCHITECTURES



Drain sw	Dummy switch	Gate switch	Source switch	Current steering	All NMOS	Fully differential current steering
Clock feed-through	charge sharing	Low speed	high speed	dif/high speed	matched PFD load	high speed high PSRR

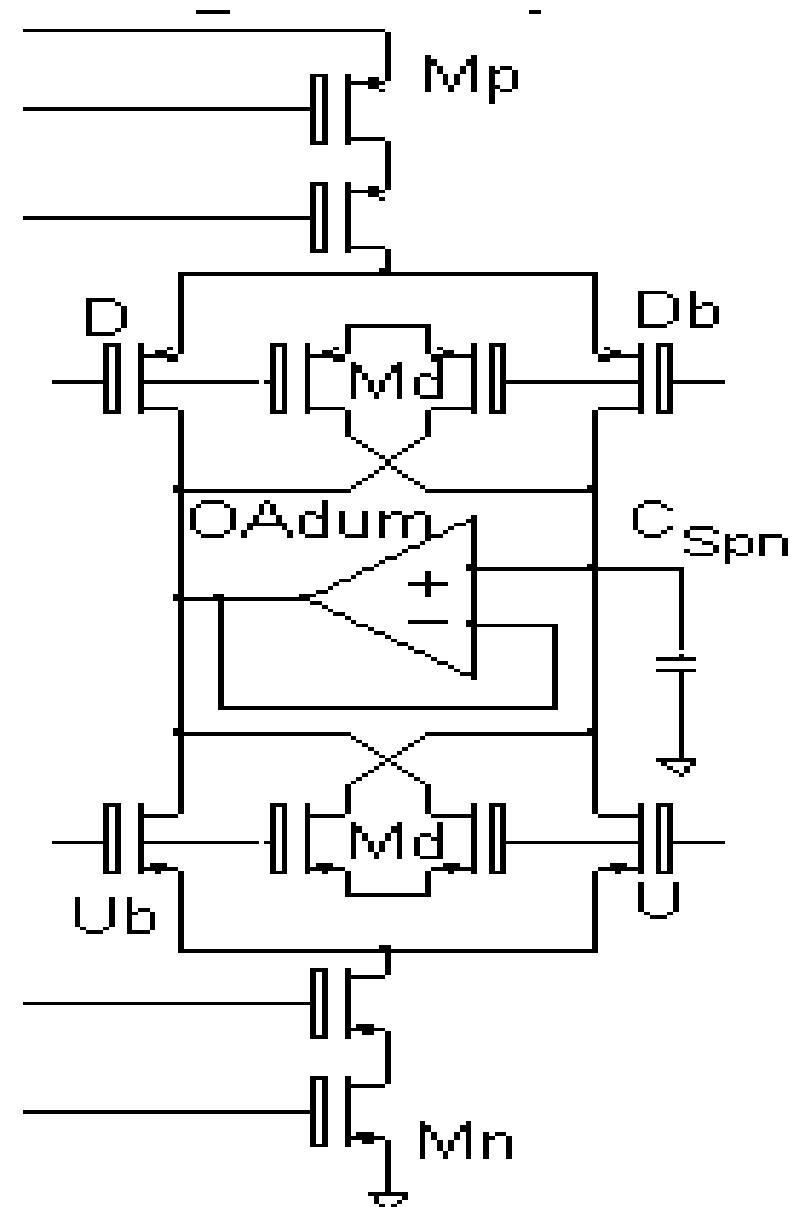
CP Charge-Injection Compensation

- Use half size devices to **compensate the channel charge-injection** → works well for very fast switching when charge splits half/half between source and drain
- For a good cancellation a good matching between up/upb/dw/dwb is required → otherwise charge is cancelled in average over one period, but VCO control voltage has ripple → increase reference spurs



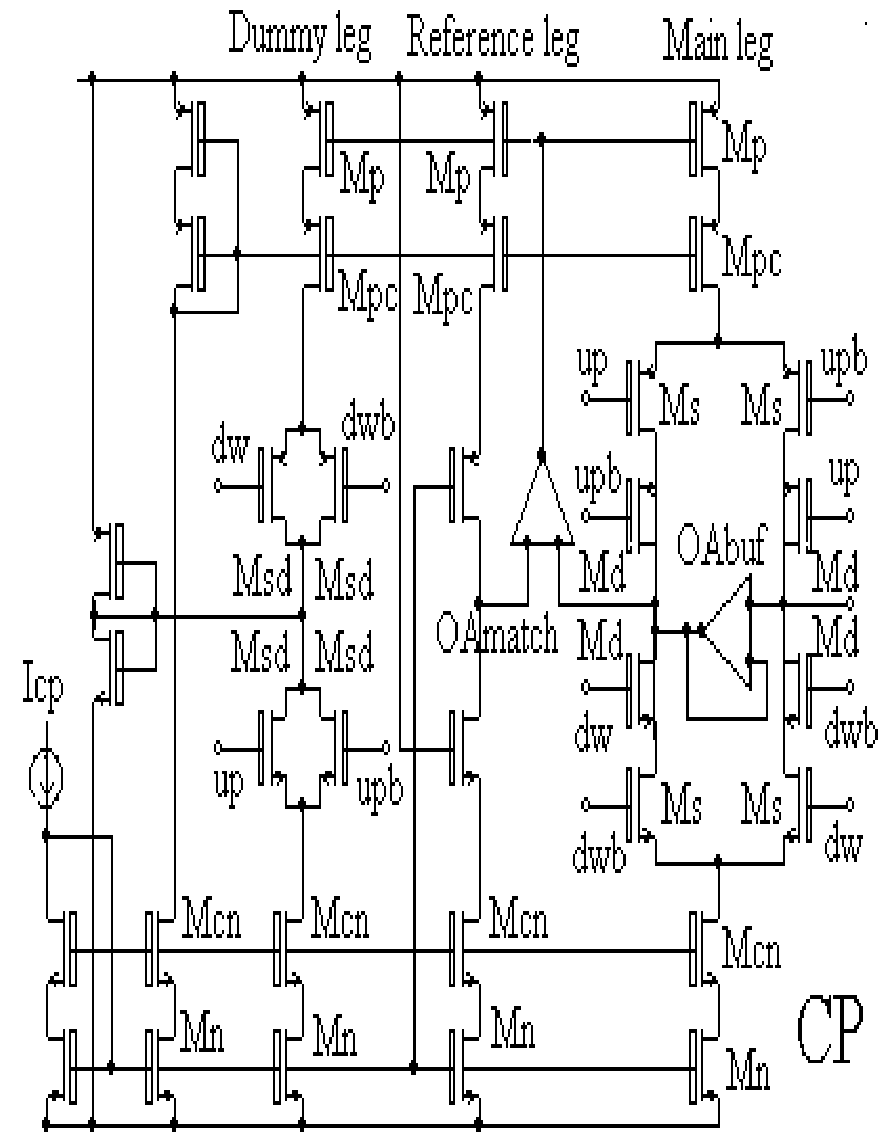
CP with Charge Sharing Cancellation

- OAbuf keep the dummy output at the same potential as the loop filter → **avoid charge sharing** from dummy side
- Use **equal size dummy switches** such that simultaneous charge-injection and clock feed-through is realized → Each output node sees two C_{gd} capacitors connected at opposite sign signals
- Not perfect cancellation of charge injection → main switches are in saturation while the dummy switches are in triode



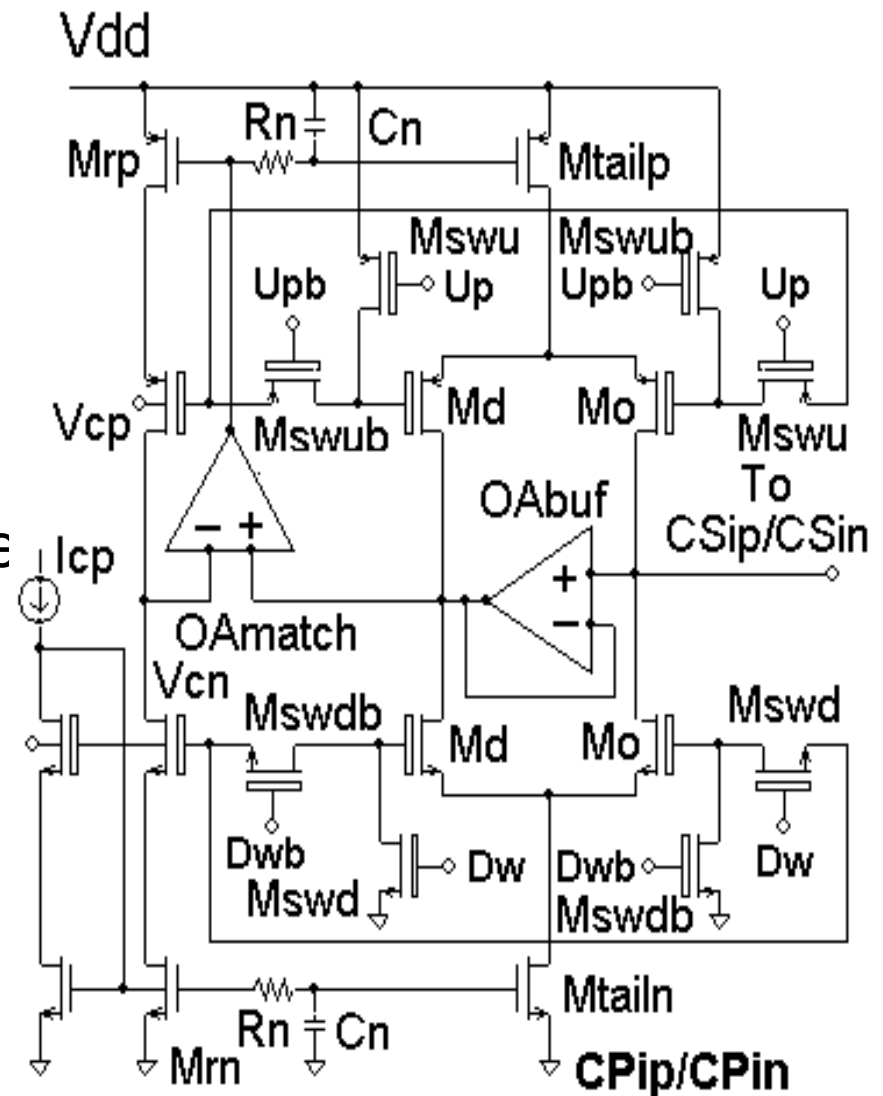
Dynamic biasing Charge-Pump

- To ensure a perfect match of up and down currents for a wide range of output voltages → use a DC feedback loop to control the PFET current mirror
- Reference voltage is taken from the dummy leg which is kept by OAbuf at the loop filter voltage
- OAmatch drives the PFET mirror such that **up and down currents are equal for all V_{ctrl} values**
- Sense node is given by a **replica current leg that is always ON**



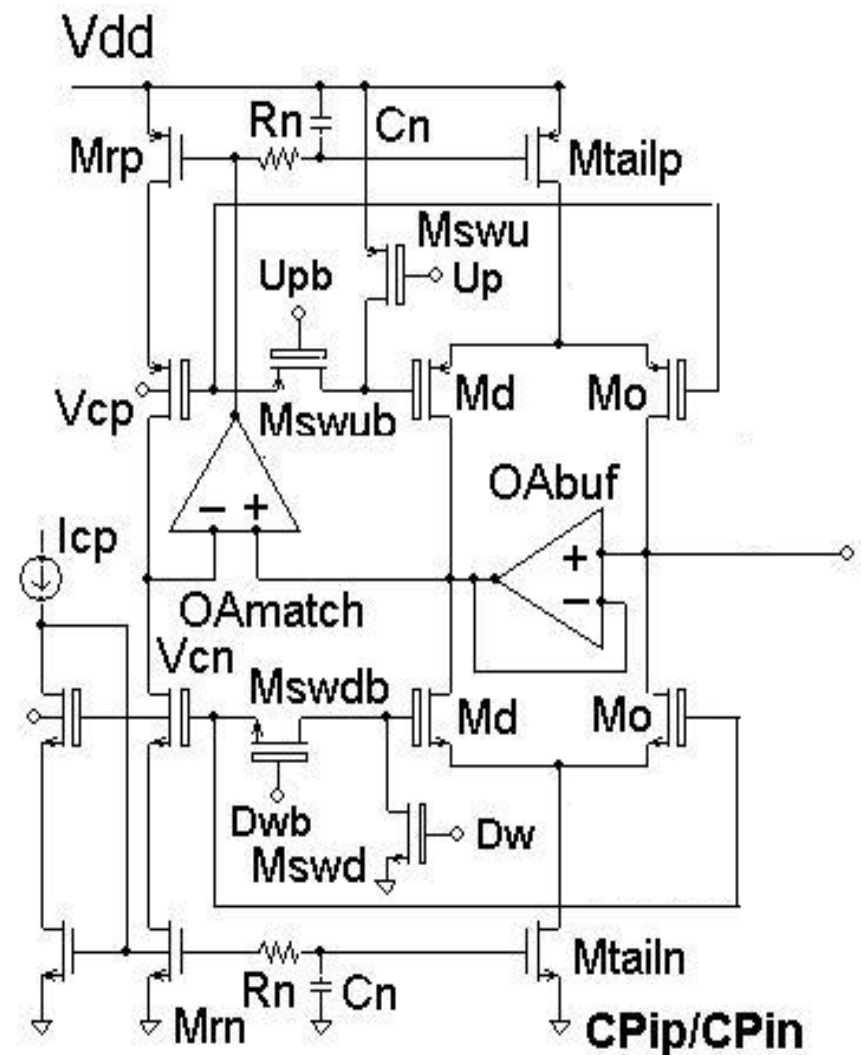
Reduced Swing Differential-in CP

- The clock feed-through depends on C_{gd} value and on the **swing of the digital control signals**
- Use a reduced swing control voltage to drive the current steering switches (between the cascode voltage and the corresponding supply line)
- The switches are operated between OFF and **ON in saturation region** → they act also as cascode devices, increasing the output impedance



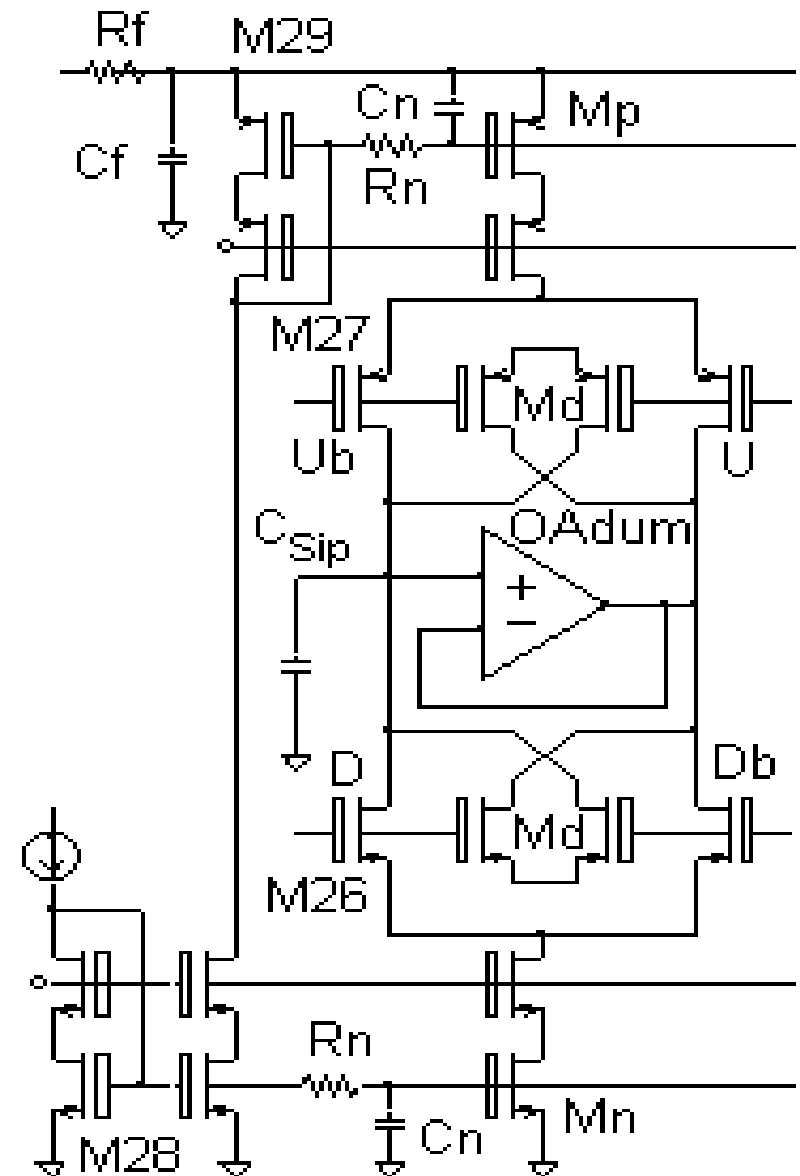
Single-Sided Switching Current Steering Charge-Pump

- The devices connected to the loop filter have their gates always connected to the constant cascode voltages → minimize clock feed-through
- The **switching devices are connected to the dummy side** of the CP
- Single sided switching works fine for medium output control voltage range, but has leakage issues for wide ranges



Charge-Pump Noise Contribution

- The CP input bias current noise is first order rejected as it is mirrored both to the up and down currents
- The up/down current mirrors have noise contributed both by their **input master devices** and **output slave devices**
- To **cut the CP noise in half** a low corner frequency **RC filter** was interposed between the master and the slave devices of the current mirrors
- Integrated noise of the master devices is reduced to KT/C



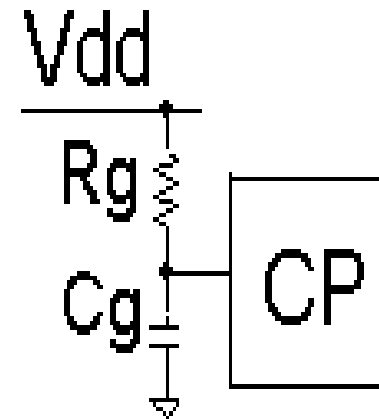
Spur Down-Conversion Mechanism

- The switching action of the charge-pump is capable of **down-converting** high frequency spurs/noise present on the supply lines (e.g. coming from another PLL or other switching circuits of the ASIC)
- If the down-converted spur falls into the bandwidth of the PLL → minimal rejection is present and the spur appears at the output low-pass filtered with f_n corner frequency
- Minimizing the spur down-conversion → requires filtering of the CP supply line

CP Supply Filtering Techniques

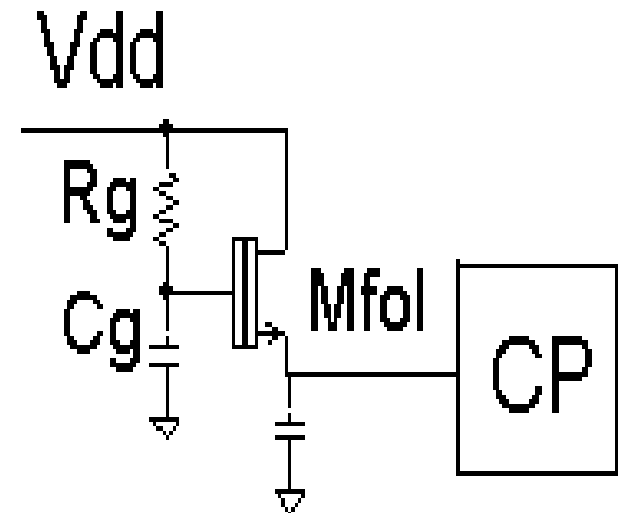
- **Passive RC filter**

- The R is limited by the headroom voltage loss
- C is limited by die area
- Pole position in MHz range



- **Active RC filter**

- Need a zero-VT FET follower to provide the load current with a minimal V_{GS} voltage drop
- R limited by the output voltage noise
- Pole position in KHz range

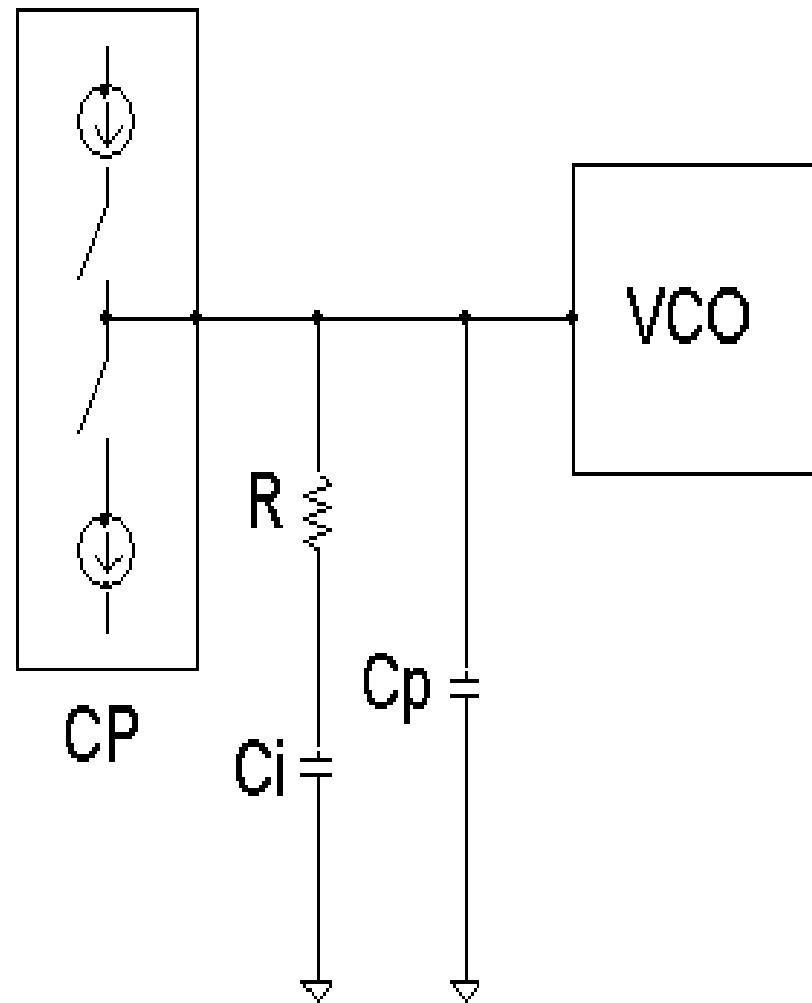


Loop Filter Requirements

- **Low noise contribution** → few active devices or passive
- **Low reference spurs** → minimize CP up/down pulses or isolate oscillator control input from CP switching
- **Low supply injected spurs** → no supply connection (passive) or use a regulator
- **Low area** → limit the total capacitors size → compromise with noise
- **Provide gain** → Active loop filter → reduce C size
- Tunable time constants → switches add clock feed-through and current leakage → limit reference spurs

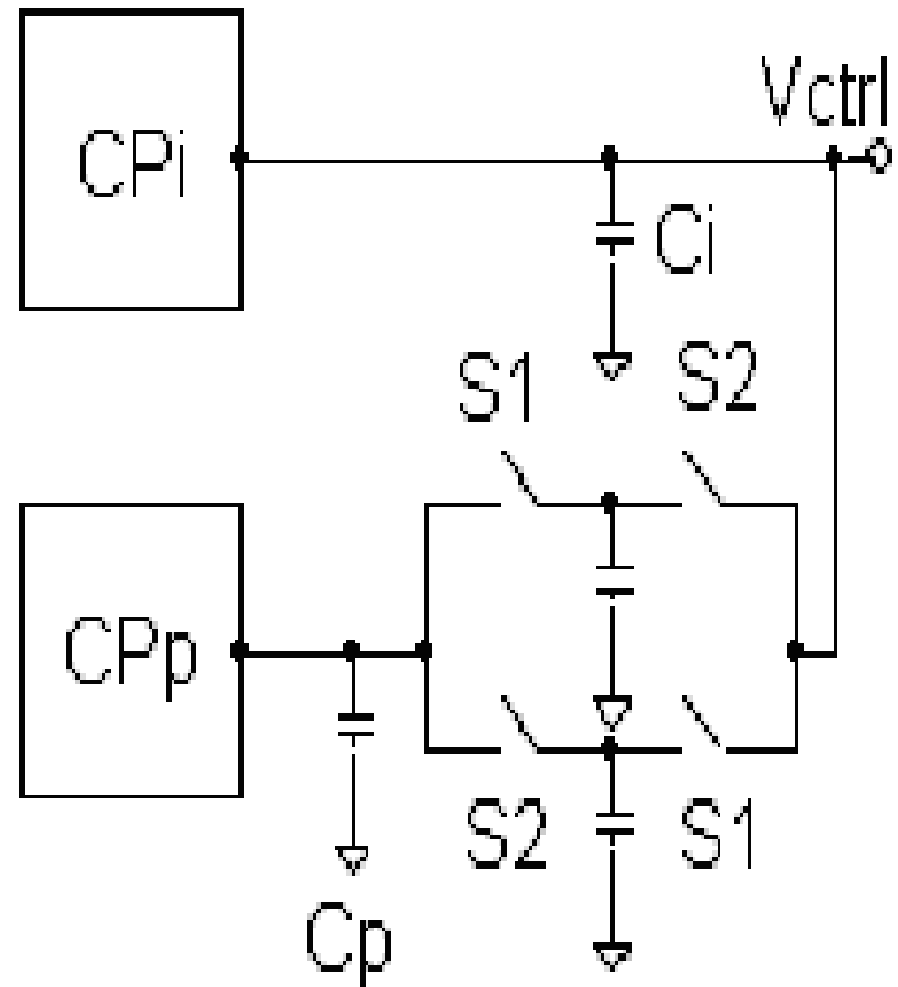
Continuous-Time RC Loop Filter

- **Simplicity** → passive configuration
- **Low noise** contribution - no active devices
- Very **high PSRR** → no supply connection
- All capacitors are connected to GND → can be implemented with MOSFETs
- Need large capacitors in low noise applications (small R to reduce noise → large C)
- Does not isolate oscillator from CP switching



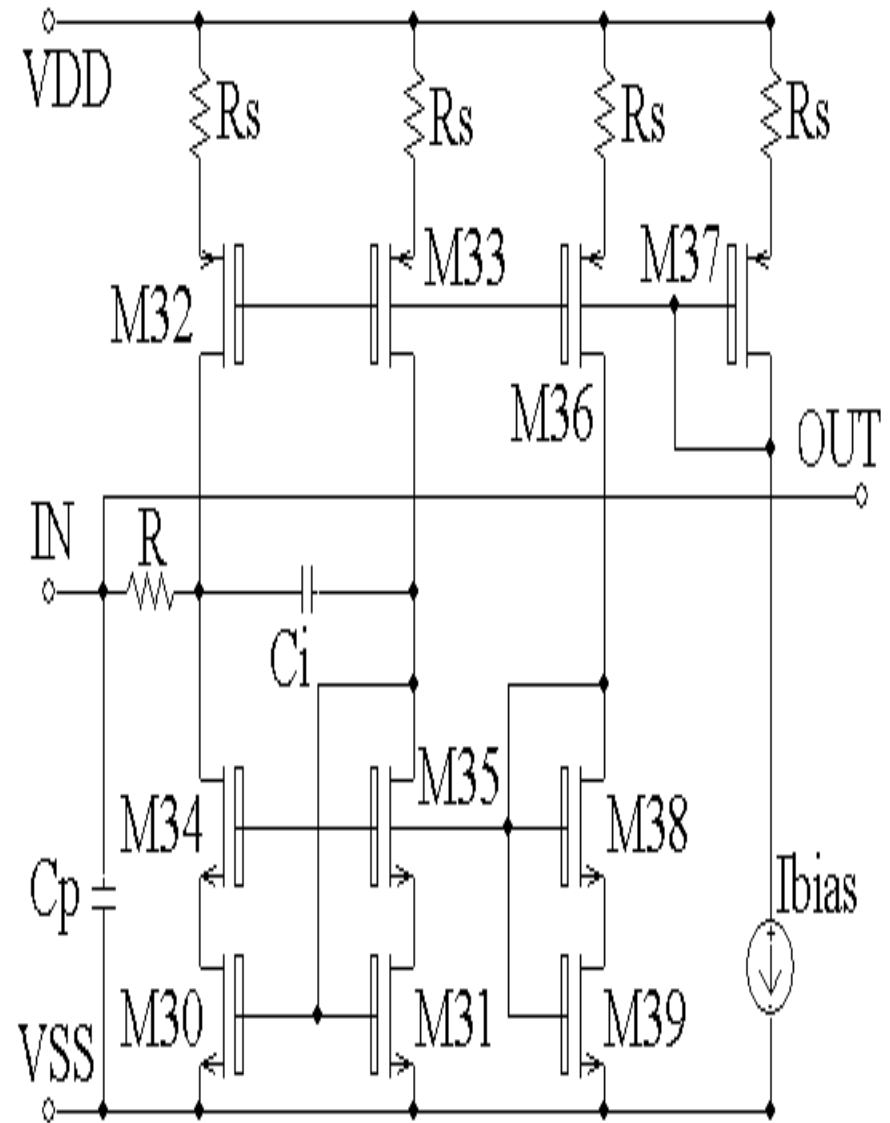
Switched Capacitor Resistor RC Filter

- To reduce the noise the stabilizing zero resistor was simulated with a switched capacitor network
- Noise is limited by $KT/C \rightarrow$ can be made small using large C
- Need 4 additional switches that may degrade reference spurs due to their clock feed-through and channel charge injection
- Keep all the other drawbacks of the standard RC loop filter



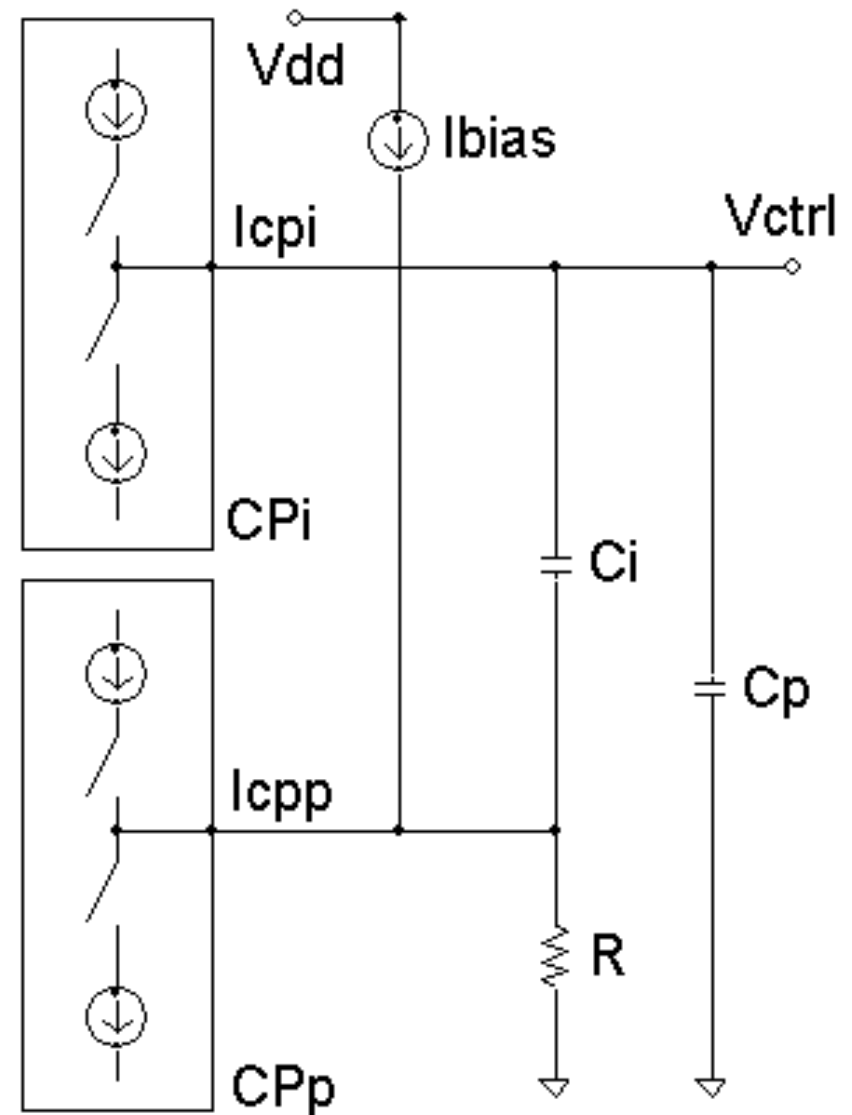
Miller Capacitor Multiplication RC Filter

- In low bandwidth PLLs the loop filter time constants are very low \rightarrow large capacitor area (several nF) that are usually implemented **off-chip**
- **Solution: Miller capacitor multiplication** $C_{eq} = C \cdot (1 - M)$ \rightarrow reduce the physical size of C and integrate it **on-chip**
- Voltage mode Miller multiplication \rightarrow hard voltage headroom issues
- Current mode Miller Multiplication \rightarrow preferred



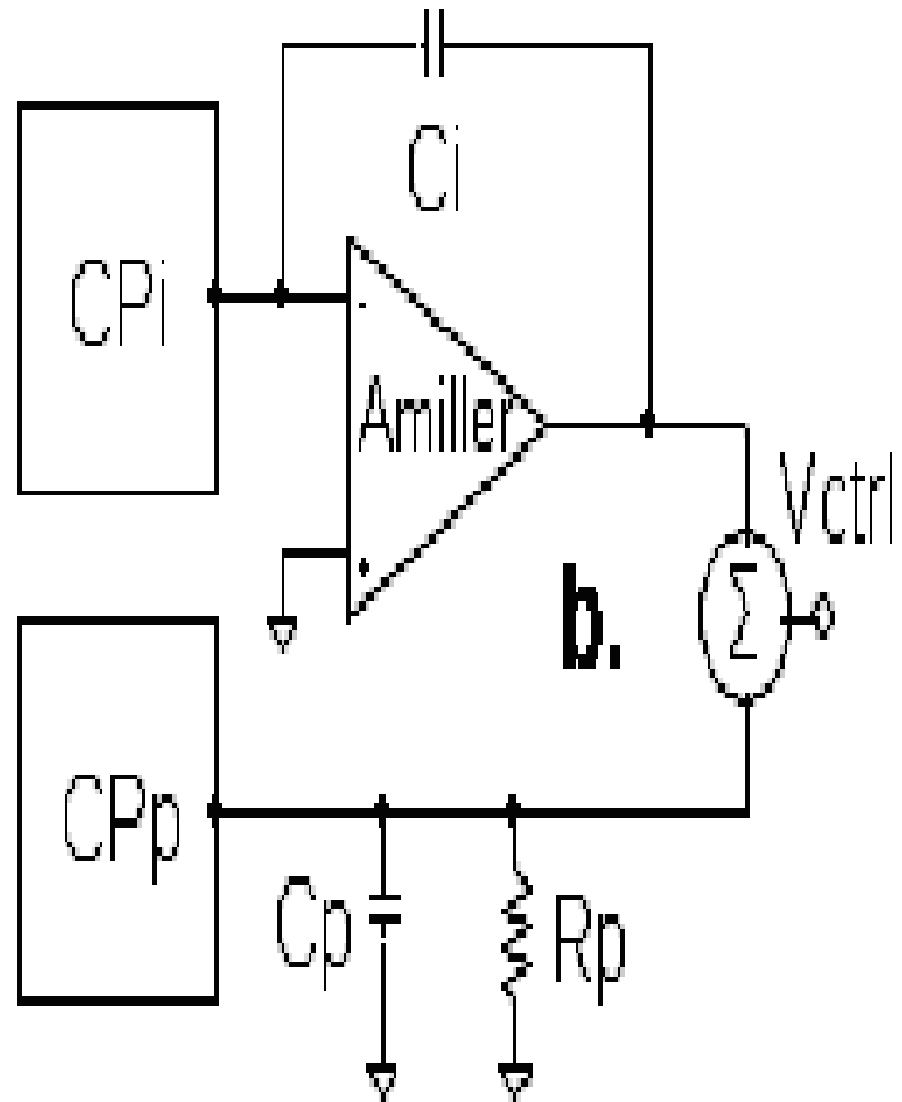
Noiseless Resistor Multiplication Filter

- Instead of multiplying C we can **multiply R** to reduce the capacitor size
- Want $R_{eq} = R * M$, but **without getting the corresponding noise** (noiseless multiplication)
- Use a second charge-pump that injects a current M times larger than the main charge-pump directly into the resistor
- R appears multiplied for the zero position, but not for the pole position → need to increase C_p by the same M factor ($C_p \ll C_i$)
- Still a passive filter → low noise contribution
- Require a **floating capacitor** → large area (MIM or Metal capacitor)



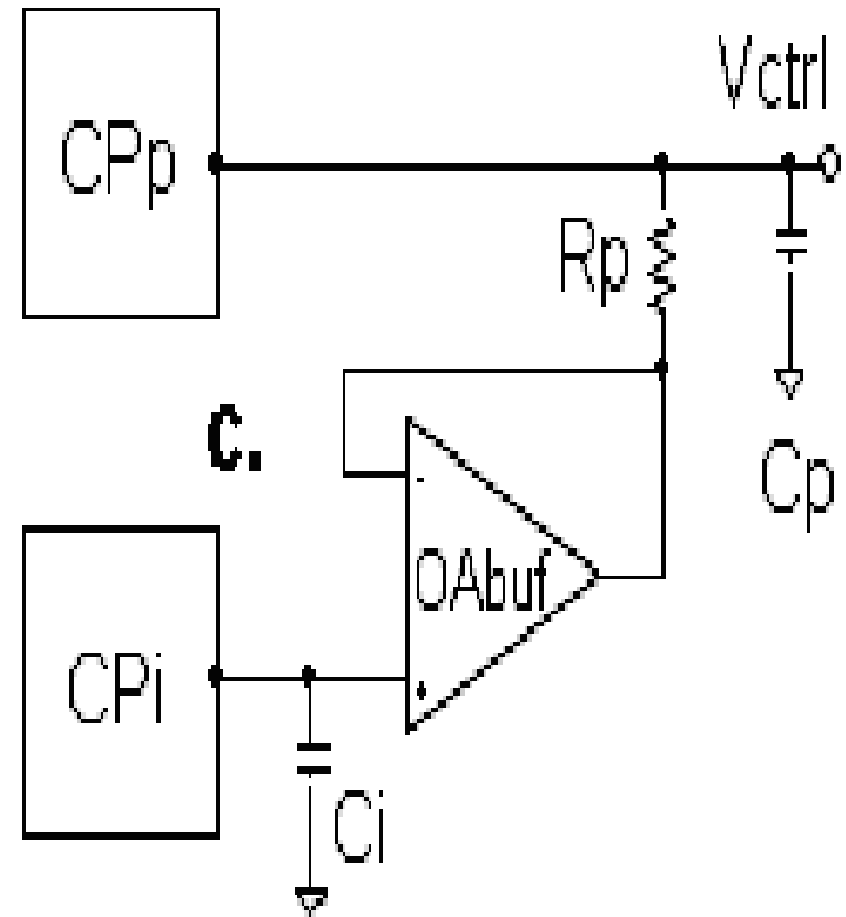
2 OpAmp V-Mode Feed-Forward Filter

- Alternative way to create the stabilizing zero → **feed-forward path**
- VCOs need a voltage-mode filter (can use or not Miller capacitance multiplication)
- C_i is reduced by the ratio of the two charge-pump currents
- Need **two operational amplifiers** → more noise and larger power dissipation
- Use active devices → PSRR is a concern



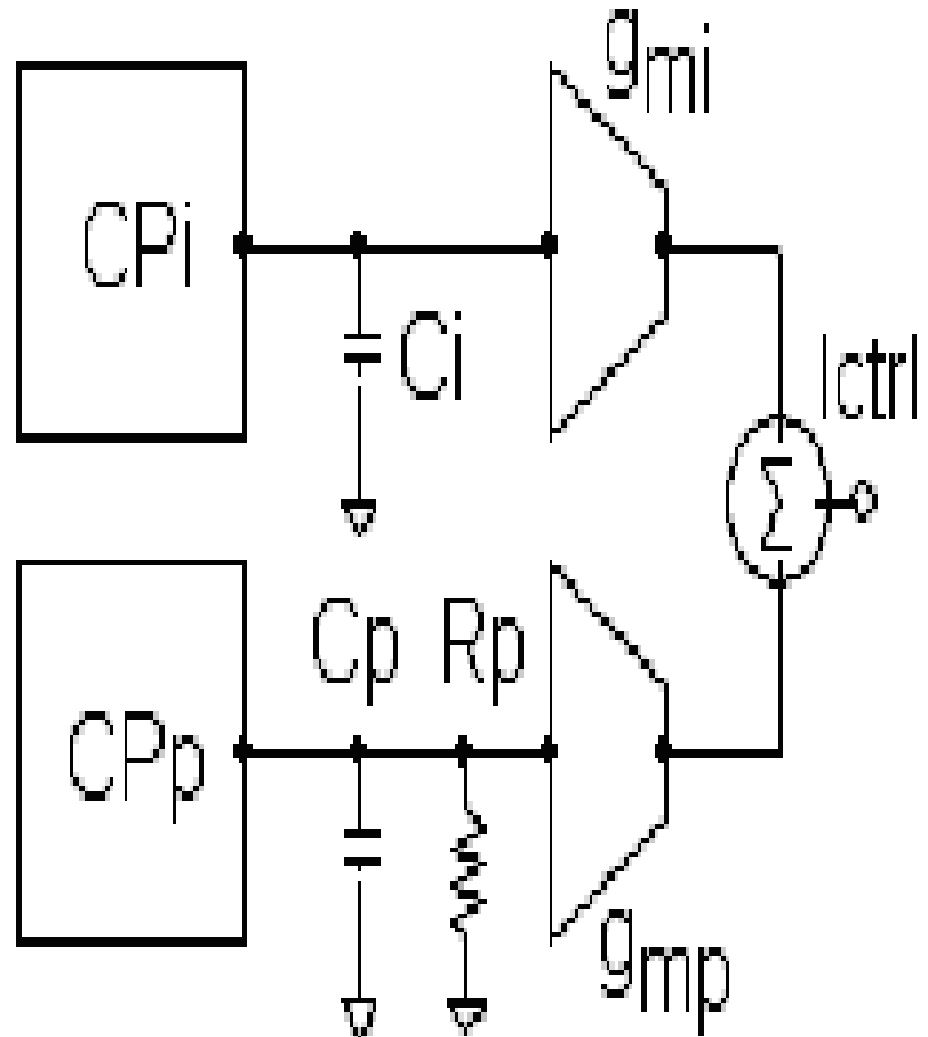
1 OpAmp V-Mode Feed-Forward Filter

- To minimize the noise introduced by the loop filter a single OpAmp architecture was developed
- The OAbuf isolates the C_i capacitor from the proportional path (leakage current)
- The **summation** is done by **connecting in series** the integral and proportional voltages



Current-Mode Feed-Forward Filter

- Appropriate for ICO PLLs
- The integral and proportional control currents are summed directly at the output node without the need of a summing amplifier
- The integral and proportional transconductance stages can be made low noise by using **large source resistor degeneration**
- For VCO based PLLs an output resistor is used to convert back to voltage (large current for low noise)

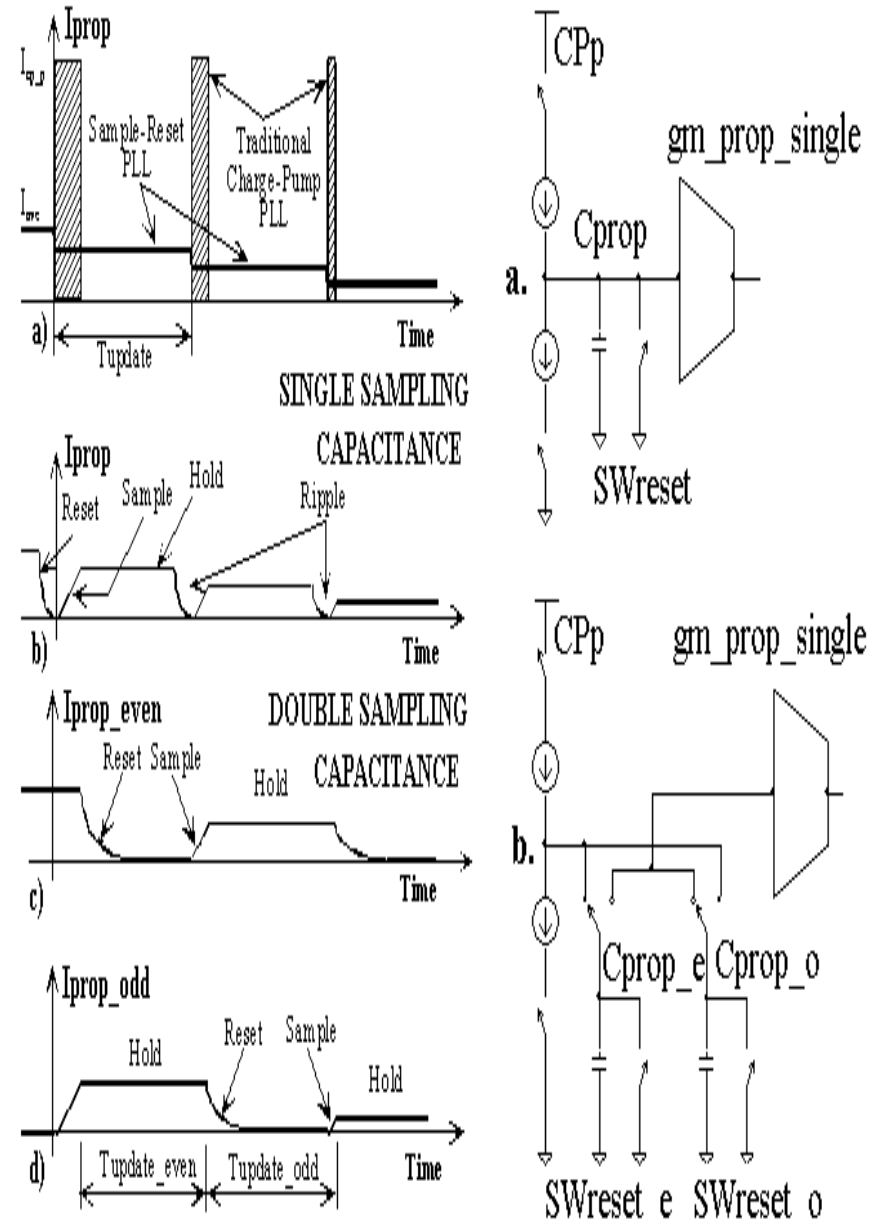


Reduce the PLL Reference Spurs

- **Solution 1:** reduce the up/down pulse width (require a fast switching CP and fast reset PFD) → spurs as low as -60dBc
- **Solution 2:** isolate the oscillator from the charge-pump switching and distribute the proportional control energy over an entire reference clock period → use a sample and hold proportional path (ref. spurs -70..80dBc)
 - Measure the phase difference
 - Apply a constant proportional control signal
 - Reset the proportional path each reference cycle

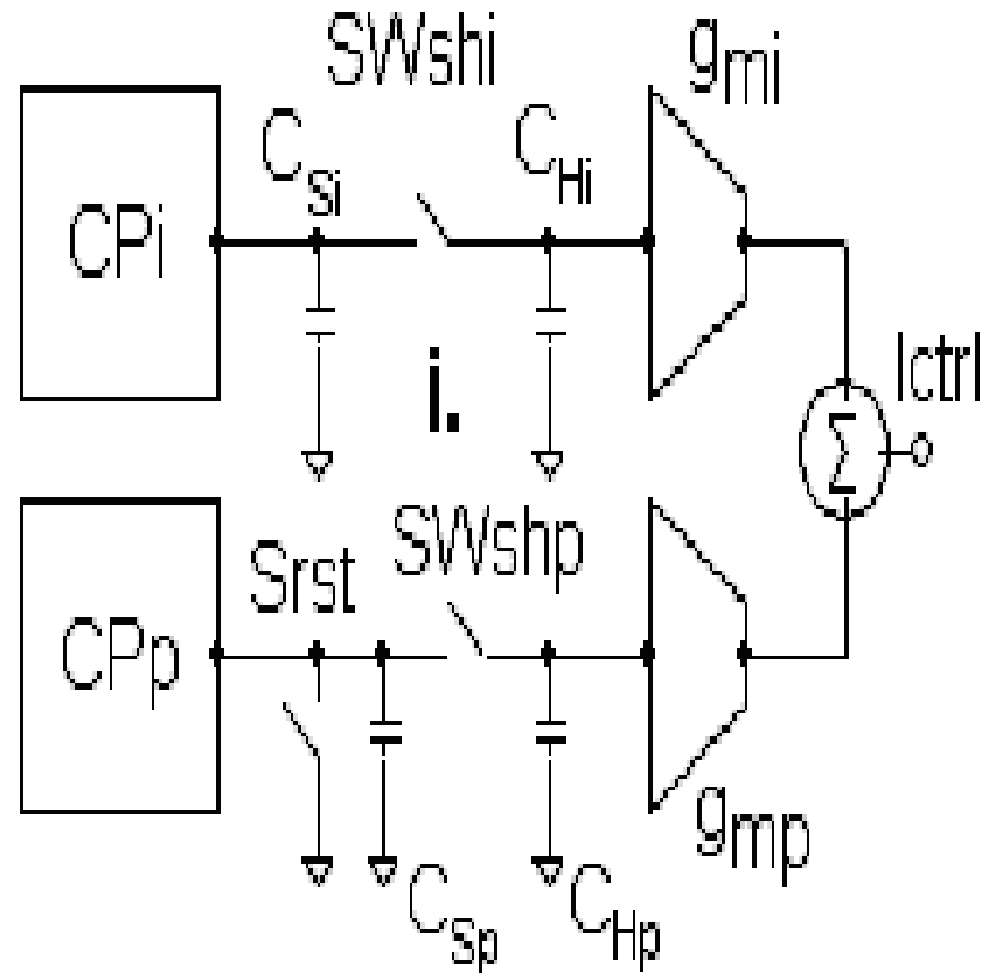
Hybrid Continuous-sampled loop filter

- Only the proportional path is implemented with a sampled structure (higher charge-pump current)
- Need to **separate** the phase sampling and reset operations from the phase holding → provide a continuous control signal to the oscillator → dual proportional path operated in tandem → 2 CPs
- The ripple pole is still implemented with a continuous time RC filter → add some extra noise



Fully sampled loop filter

- For best reference spurs rejection **both** integral and proportional paths need to use sampled configurations
- If a higher crystal oscillator frequency is available than a different architecture can be used to provide a continuous oscillator control signal – isolation windowing
- The oscillator is isolated only for a $\pm\Delta T_{ref}/M$ time period around the reference clock active edge (small phase offset when in lock)
- Digital pole \rightarrow lower noise

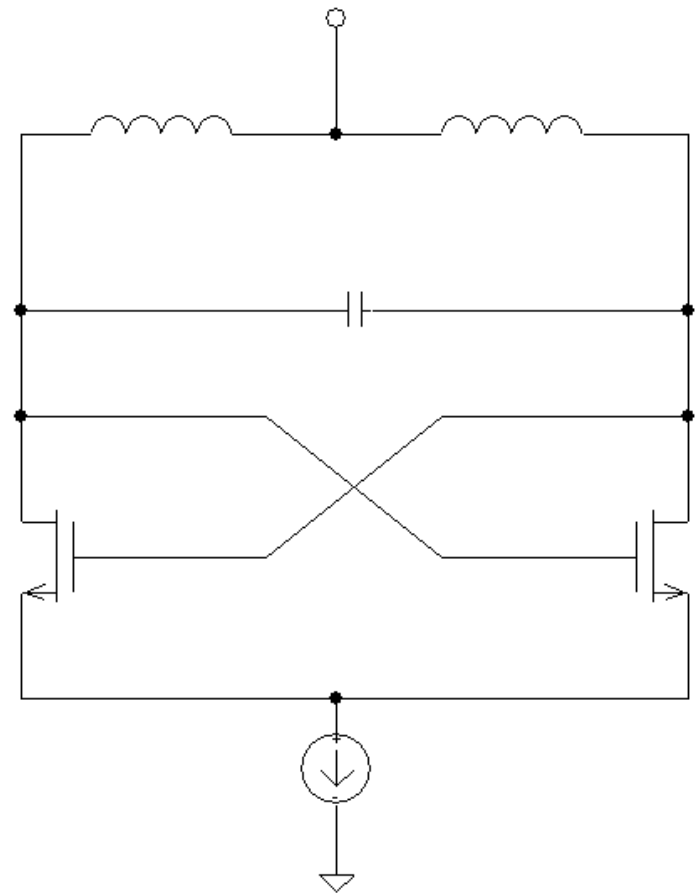


LC Oscillator Requirements

- Integrated oscillators need a differential amplifier → reduce the **supply and substrate noise** sensitivity
- **High frequency operation** → minimize parasitic capacitances
- **Low oscillator gain** → reduces both output clock phase noise and spurs → requires a wide range control signal
- Good **symmetry** of the waveform → lowers 1/f noise up-conversion
- Reduce the noise coming from the tail bias current
- Minimize supply voltage dependent capacitors connected to the tank → minimize supply pushing

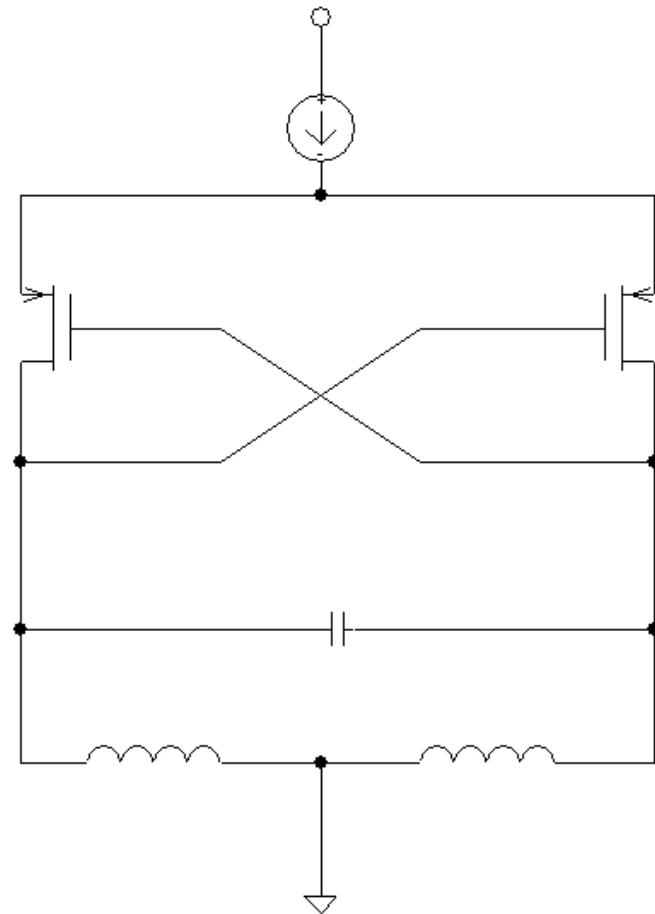
NMOS differential amplifier VCO

- Lower size devices for a given gm requirement → operate at higher frequency
- Higher oscillation amplitude → low phase noise
- Requires a mid-point in the inductor to bias the circuit
- NFETs have larger $1/f$ noise which degrades the $1/f^3$ oscillator phase noise
- Hard to ensure the tank symmetry if bondwire inductances are used



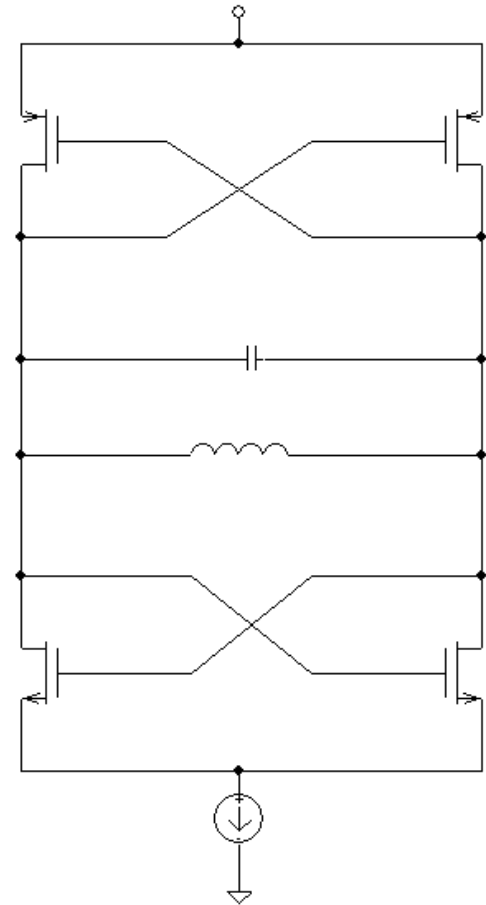
PMOS differential amplifier VCO

- PFETs have much lower $1/f$ noise (due to their buried channel) → achieve a much lower $1/f^3$ phase noise
- Need a higher current in comparison with the NFET VCO
- Need larger size devices → lowers the maximum operating frequency
- Need a mid-point in the inductor for bias purposes- not suitable for bondwire inductances



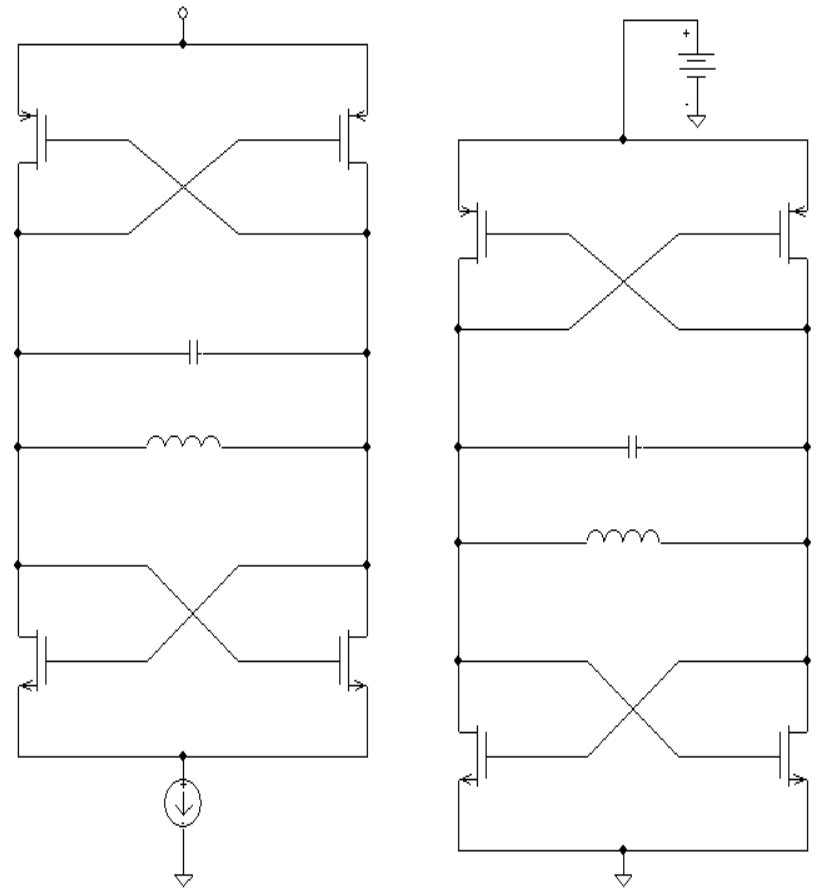
CMOS differential amplifier VCO

- Requires a lower supply current due to the stacked gm configuration
- Can use bondwire inductances as no mid-point is required
- Provide a more symmetric waveform \rightarrow lower $1/f$ noise up-conversion
- Lower Oscillator amplitude \rightarrow degrades slightly the phase noise performance



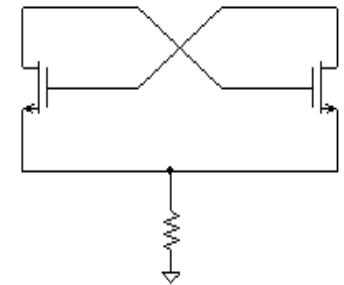
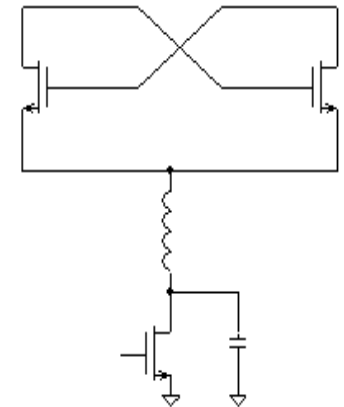
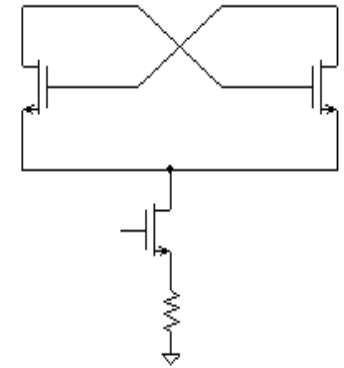
Voltage-mode versus Current-mode LC VCOs

- **Current-mode**
 - The amplitude is determined by the tail current value
 - Tail current $1/f$ noise is up-converted around the carrier
 - Does not require a precise value supply voltage
- **Voltage-mode**
 - Amplitude determined by the supply voltage value → requires a calibrated regulator
 - Does not have a tail current source → lower $1/f^3$ phase noise



Reduce the tail current Source Noise

- **Resistor degeneration**
 - Reduce both the $1/f$ and thermal noise coming from the tail source
 - Takes away headroom \rightarrow lowers the oscillating amplitude
- **LC filter at $2 \cdot f_0$**
 - Filter the second order harmonic seen by the tail current mirror
 - Effective at 1-5GHz
 - @ high frequency hard to achieve large value inductors with self-resonating frequency $> 10\text{-}20\text{GHz}$
- **Tail resistor instead of current**
 - No $1/f$ noise and lower thermal noise
 - Calibrated resistor to set amplitude

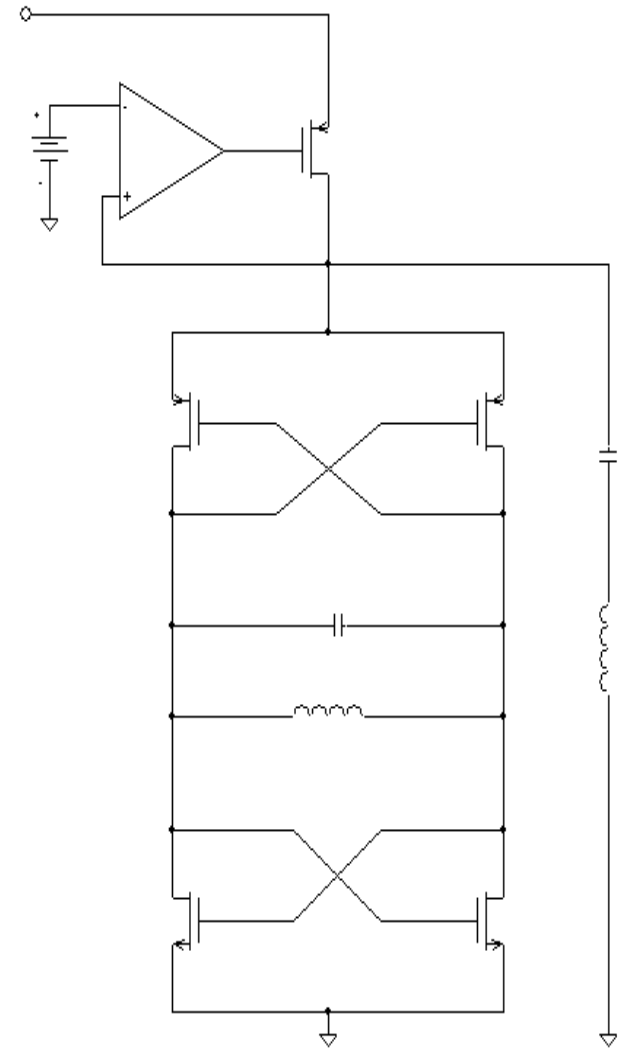


Bondwire versus Planar Inductors

- **Bondwire inductors:**
 - No additional process steps
 - Highest Q available = 40-50
 - High self-resonating frequency >20GHz
 - Limited value (0.2-0.3nH if bonding between two pads, 1-3nH if bonding from the die to the package and then back to the die)
 - Poor symmetry if a mid-point is required for bias
- **Planar inductors:**
 - Can provide a well controlled mid-point for bias purposes
 - Lower Q=10-20 due mainly to substrate losses
 - Lower self resonating frequency due to parasitic cap.
 - Need supplementary processing steps to be added to standard CMOS (use thick metal layers)

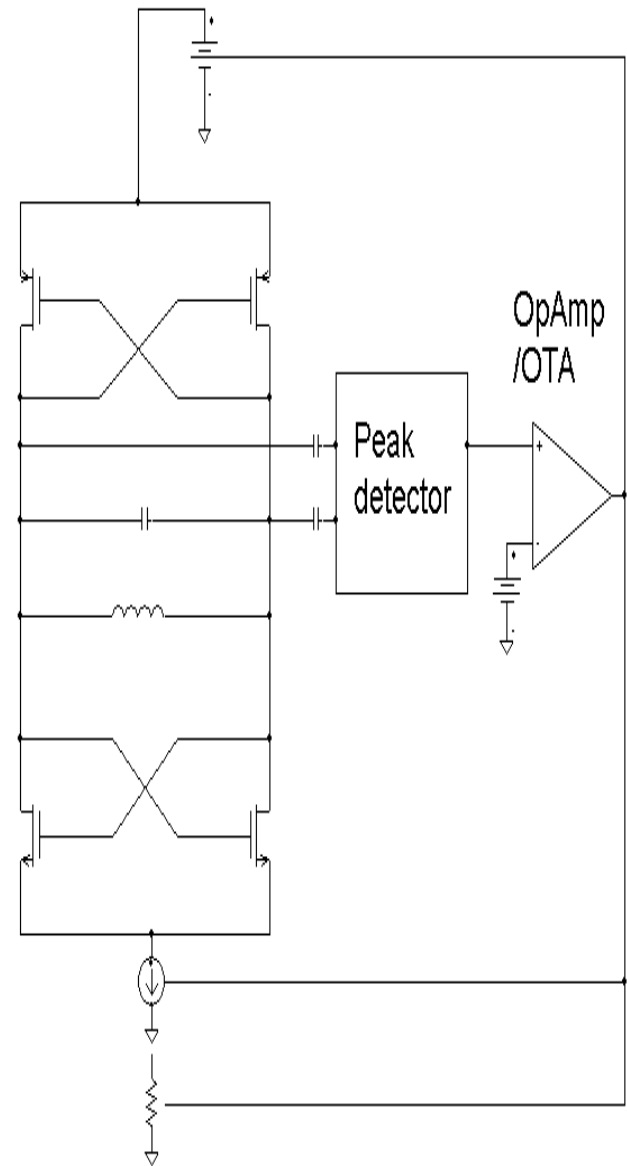
Supply Voltage Requirements

- Spurs in the LC oscillator supply line are up-converted around the carrier → need a high PSRR reg.
- Noise on the supply lines is up-converted into phase noise skirts → need a low noise regulator
- To minimize second order harmonics on oscillator supply → use a series LC circuit which resonates at $2 \cdot f_0$
- Using a MIM capacitor and a bondwire inductance provides a sharp attenuation



Automatic Amplitude Control Loop

- Maintain the maximum oscillating amplitude allowed by the available supply voltage → optimize phase noise
- AAC loop degrades phase noise
- Use a high frequency peak detector to measure amplitude
- Use an amplifier to compare the amplitude against a reference voltage (need to be low noise)
- Adjust the element that sets the amplitude (current, resistor or voltage)



Reduce the Phase-Noise of the AAC

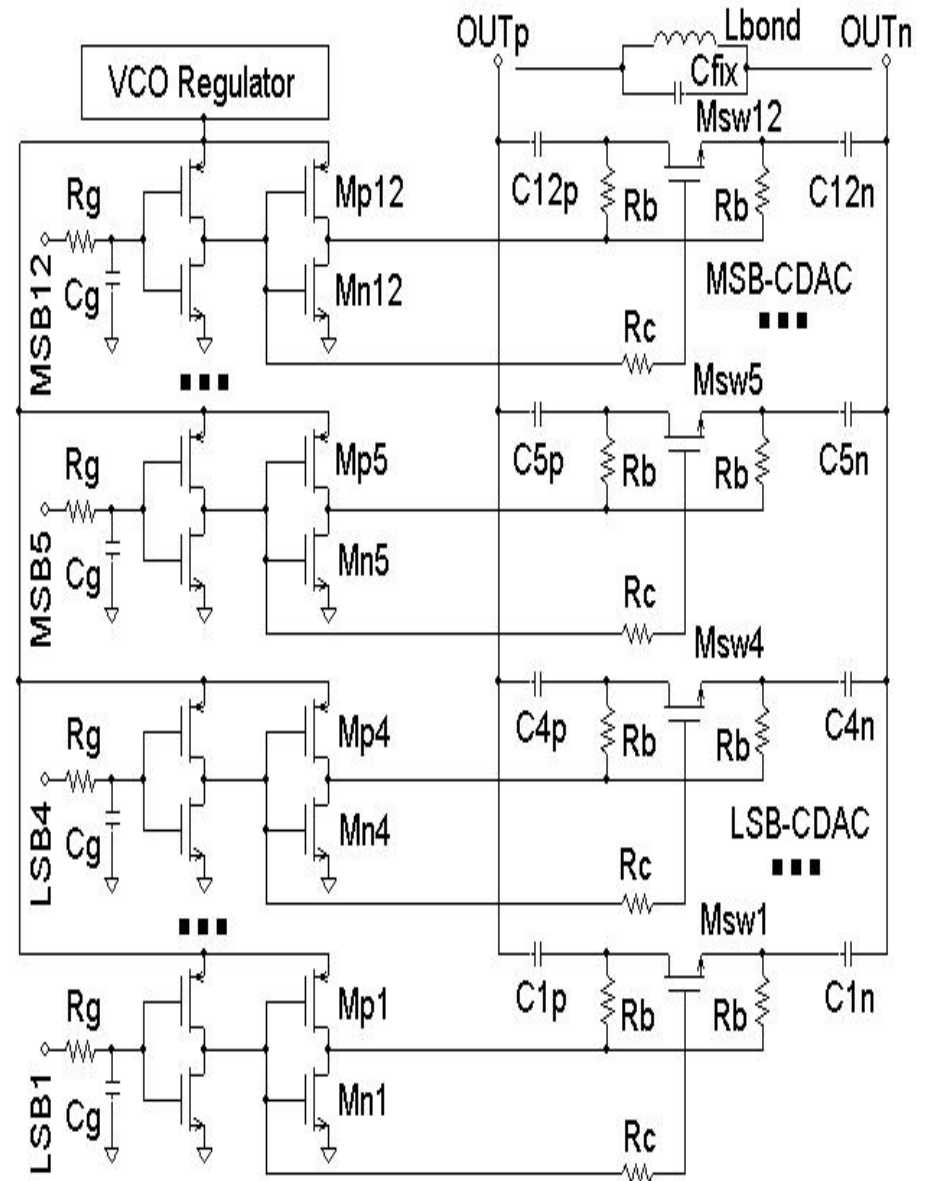
- **Continuous time AAC loop:**
 - Use PFET stages in both the AAC amplifier and the peak detectors (less $1/f$ noise)
- **Hybrid continuous-discrete AAC loop:**
 - Close the loop only at discrete times (e.g. at power-up to compensate the process variation, and in the blind spots of the communication link to compensate both process and temperature variations)
- **Discrete time AAC loop:**
 - Eliminate the noise of the amplifier by replacing it with a digital state machine

Reduce the Oscillator Gain

- Achieving a large tuning range while having a low oscillator gain requires frequency calibration → not for fast frequency changing PLLs (e.g. frequency hopping synthesizers)
- First the frequency is calibrated in **open-loop** using a capacitor DAC connected in parallel with the LC tank → bring the frequency to within few % of the target value
- The final frequency tuning is realized in **closed-loop** using a PLL loop that controls a low tuning gain varactor

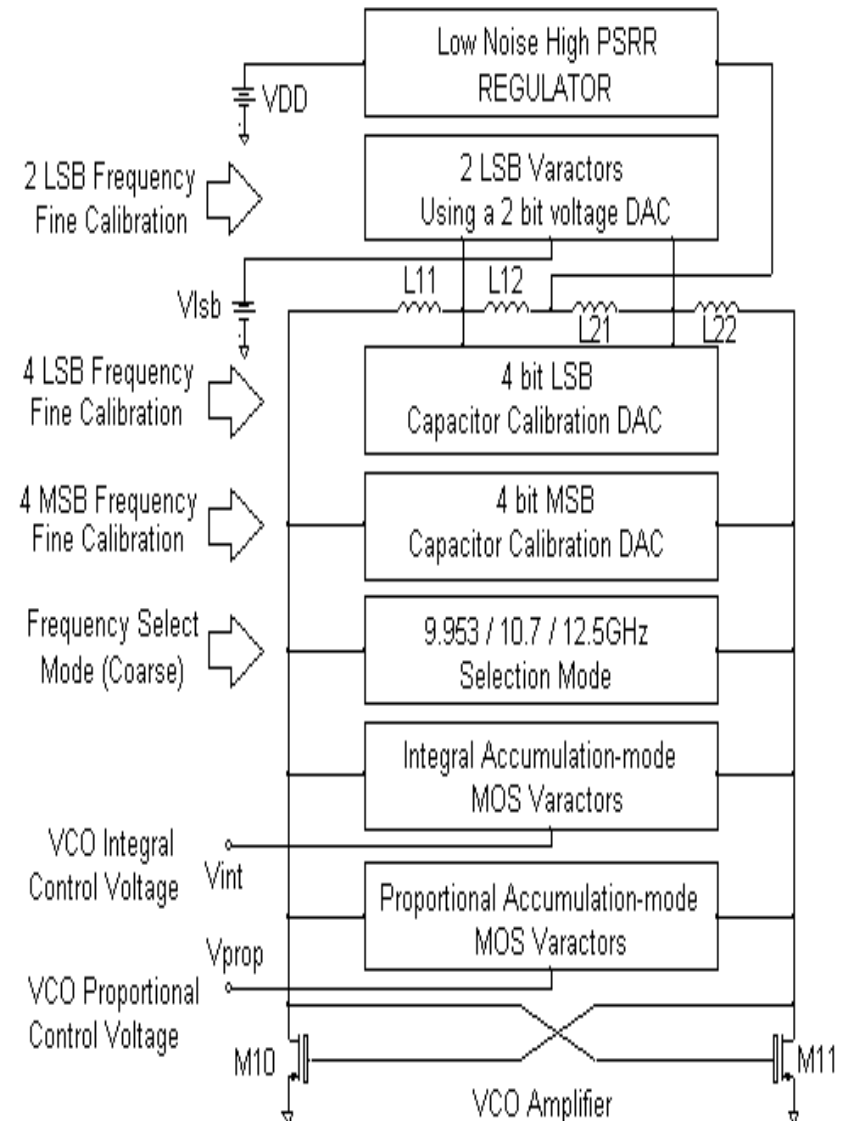
Calibration Capacitor DAC

- Use a differential capacitor → better tank symmetry
- Floating switch → 1 FET → lower R_{on} and less parasitic capacitors
- Reduce R_{on} by **pulling to GND** the drain/source of the OFF switch
- Reduce C_{jd}/C_{js} by **pulling to V_{reg}** the drain/source of the ON switch
- R_b keep floating the capacitor that is switched-off the LC tank
- R_c reduces the impact of the C_{gs} and C_{gd} capacitances



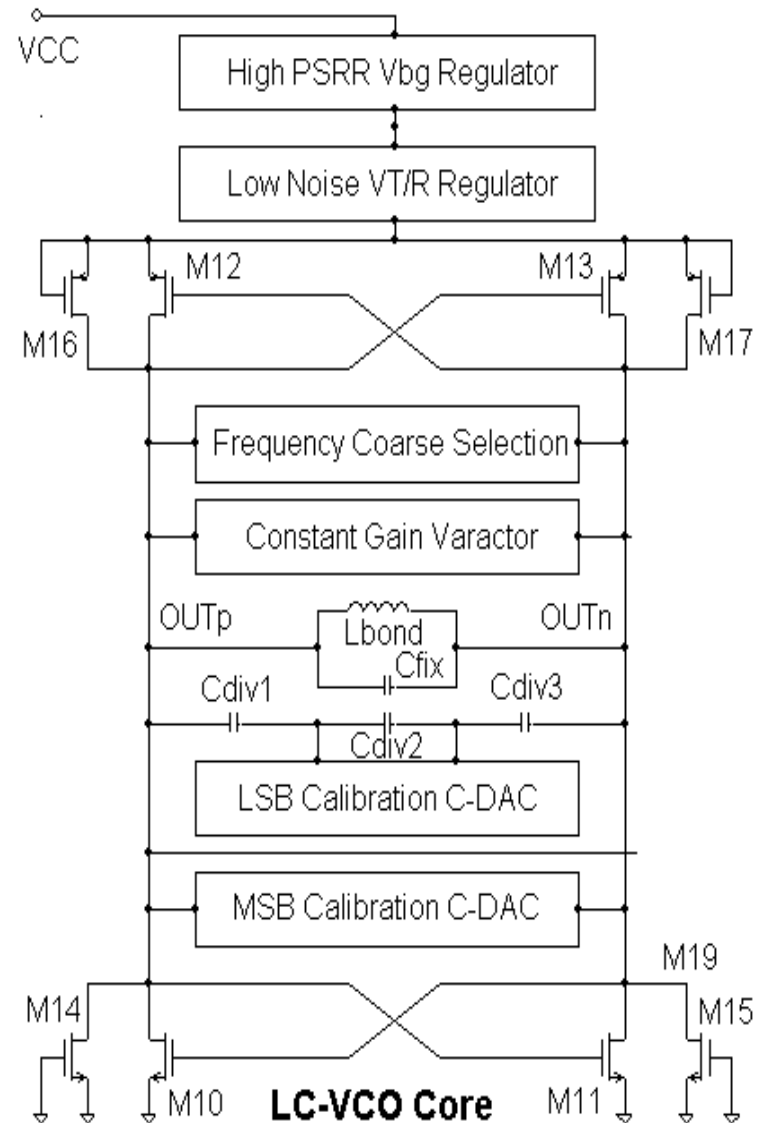
Improve Capacitor DAC Resolution

- Divide the C-DAC in a MSB and a LSB DAC → achieve 10-12 bit resolution that brings the frequency within 0.1-0.5% of the target value
- Use a **tap in the inductor** to connect the LSB C-DAC → LSB capacitors reduced when reflected on the tank
- Valid only for **planar** inductor LC oscillators that can have tap points



Improve Capacitor DAC Resolution

- Use a **tap in a capacitor divider** to connect the LSB C-DAC → suited for bondwire inductance LC oscillators that do not have taps in the inductor
- The LSB capacitors appear reduced when reflected on the LC tank
- Need to provide DC bias to the floating nodes between capacitors → avoid device breakdown

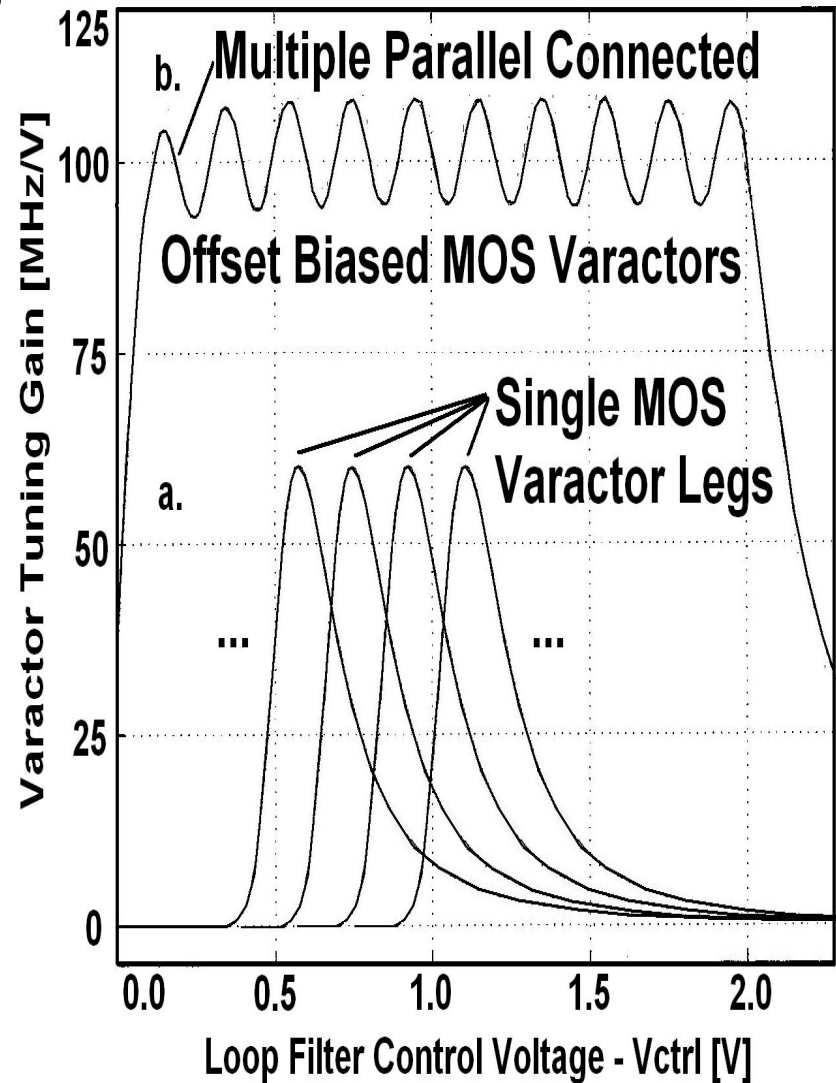


Varactor Used in LC oscillators

- **Reverse biased diode varactors**
 - Relatively poor quality factor at multi-GHz frequencies ($Q=5-10$) due to the series resistance of the non-depleted silicon layer $R(\text{freq})$
 - Highly non-linear $C(V)$ characteristic
- **Accumulation MOS capacitors**
 - Higher quality factor at high frequencies $Q=10-20$
 - Larger process and temperature variation → need a wider range open-loop calibration
 - Highly non-linear $C(V)$ characteristic

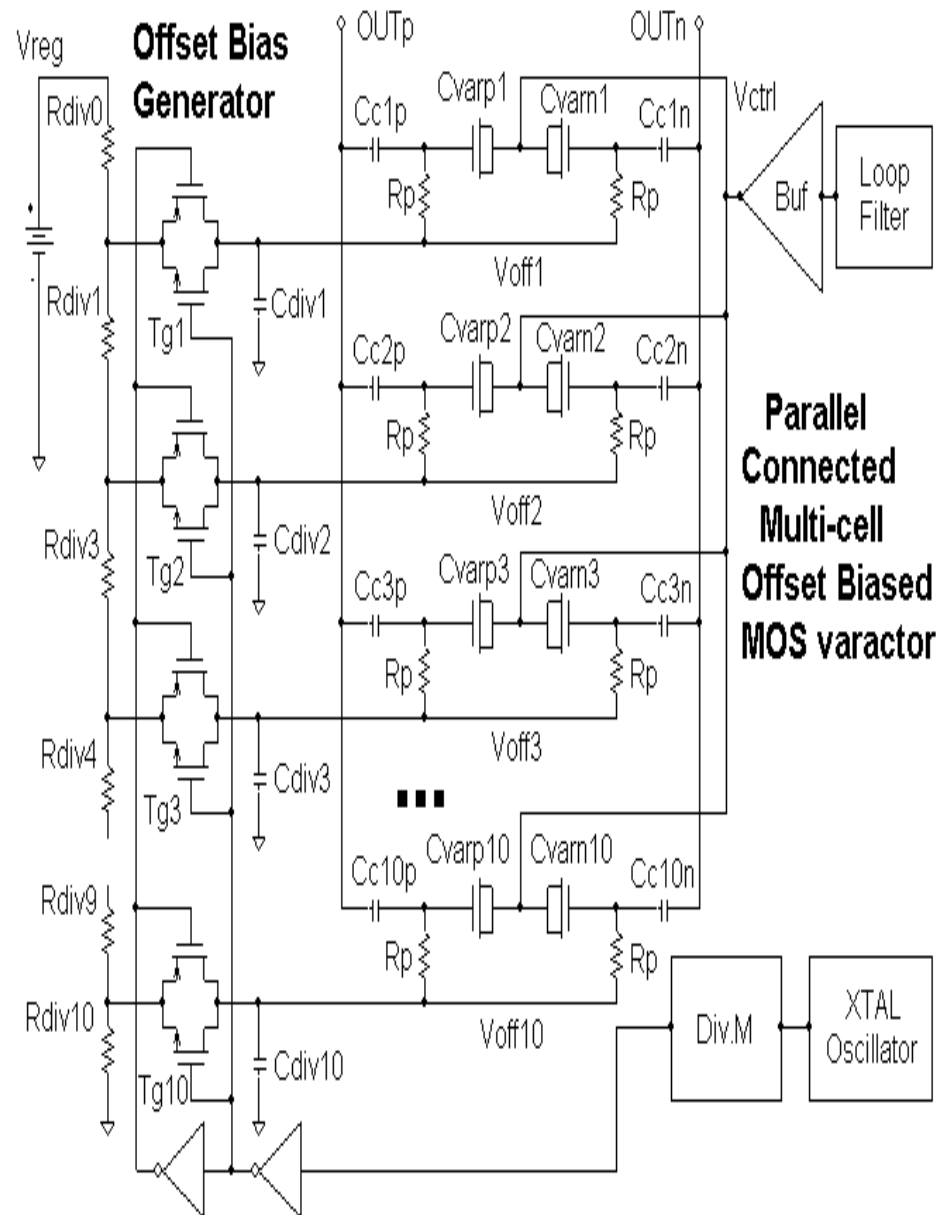
Constant Gain Varactor

- Use several accumulation MOS capacitors connected in parallel which have their DC bias shifted such that their **peak gain points are uniformly distributed** over the entire control voltage range
- **Gain ripple** depends on the number of cells connected in parallel
- The different DC offset voltages for the parallel varactor legs can be generated with a simple resistor divider biased from a low noise voltage



Constant Gain Varactor - Continued

- The noise of the resistor divider can dominate the oscillator phase-noise
- Adding filtering capacitors to limit the noise to KT/C requires a large capacitor area
- Use a **switched capacitor biasing** network controlled by a divided down reference clock
 - Low capacitor area (limited by KT/C)
 - Negligible phase noise contribution from the offset voltage generator

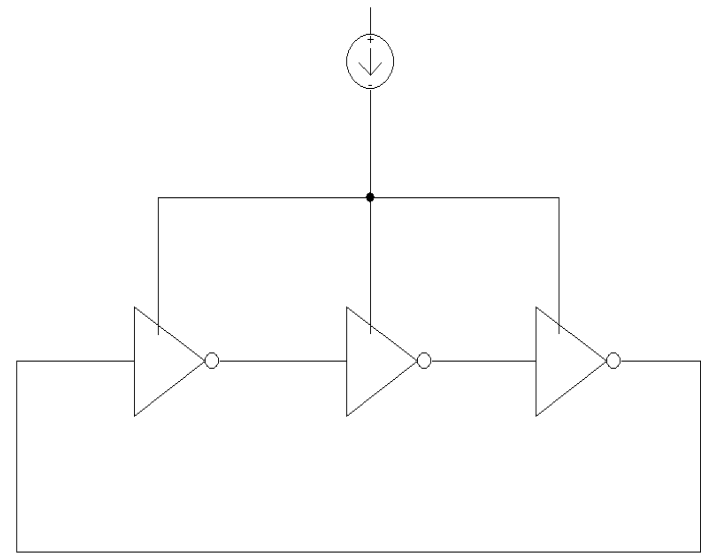


Ring Oscillator Requirements

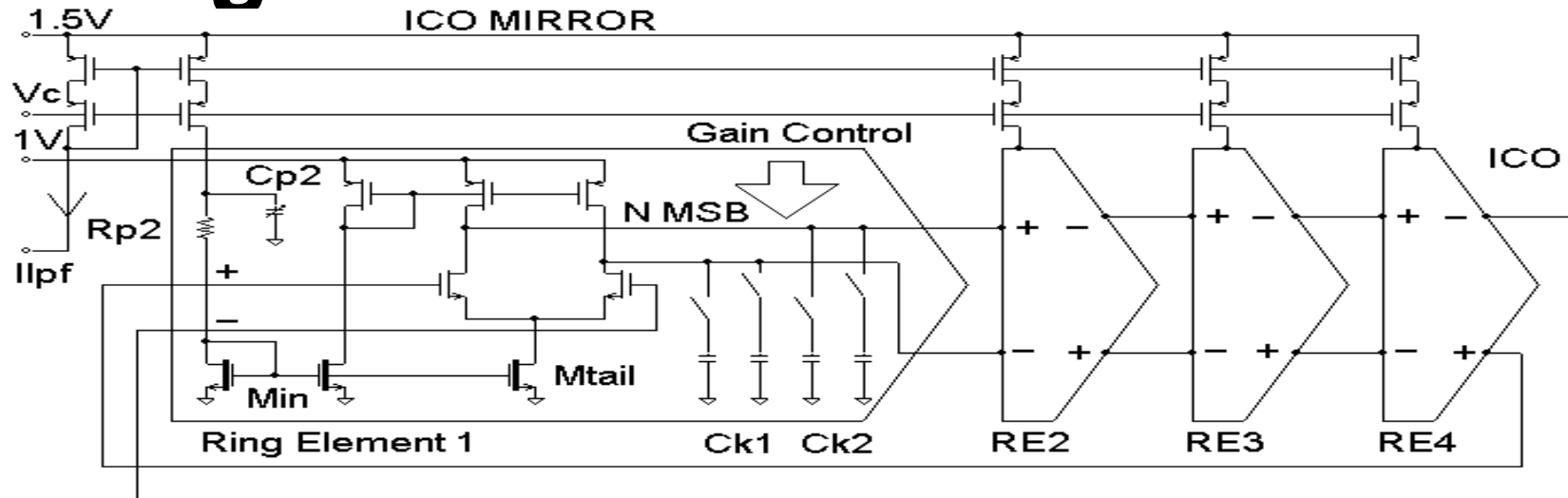
- **Operate at GHz frequencies** → minimize the number of stages in the ring (4 – provide quadrature outputs, 3 – safe operation, 2- highest frequency, but need extra phase shift)
- Have a **wide tuning range** (several GHz) → result in a **very large VCO gain**, which increases the sensitivity to PLL front-end noise and spurs
- Minimize noise coming from biasing circuitry
- Need a high PSRR, low noise regulator to avoid supply noise and spurs injection

Single-Ended versus Differential

- Single-ended inverters offer a **lower intrinsic noise** due to a **lower device count** and also a **lower power consumption**
 - Better in **SOI processes** that have negligible substrate capacitances
- In large mixed analog-digital ICs the supply and substrate noise and spur injection dominate
- Differential inverters offer better supply and substrate rejection

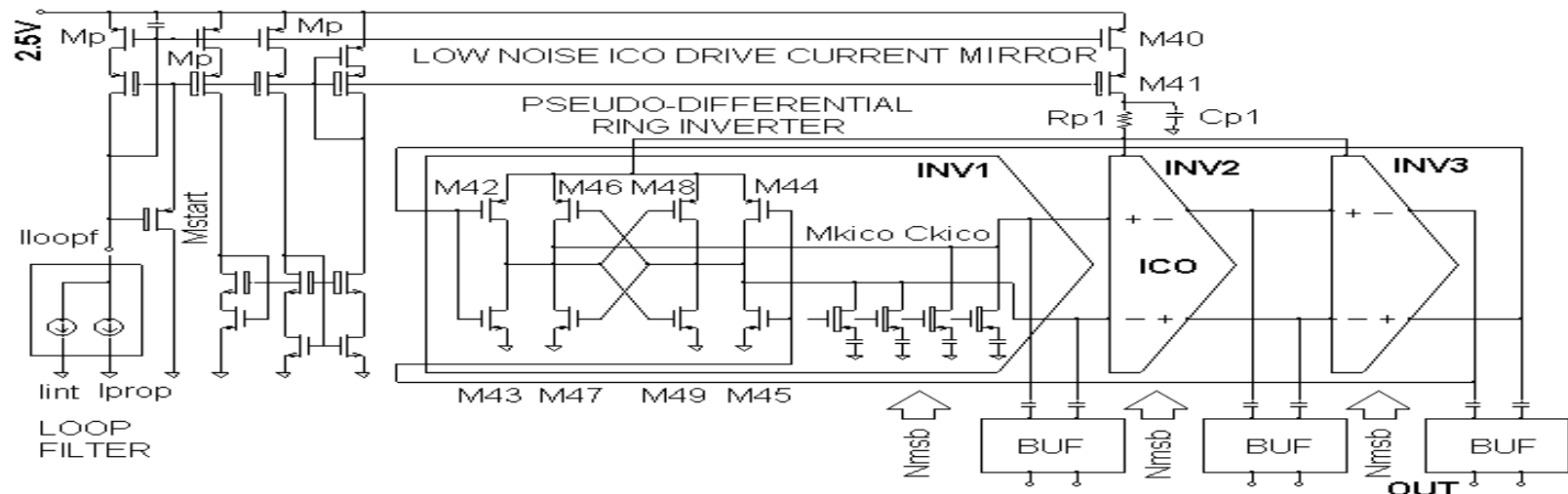


Single-Ended versus Differential



- Differential inverters give a more symmetric waveform → reduces 1/f noise up-conversion
- **Less supply and substrate injection** particularly in balanced load differential stages
- They have a **larger active device count** → more intrinsic noise
- Need larger supply current for a given operating frequency

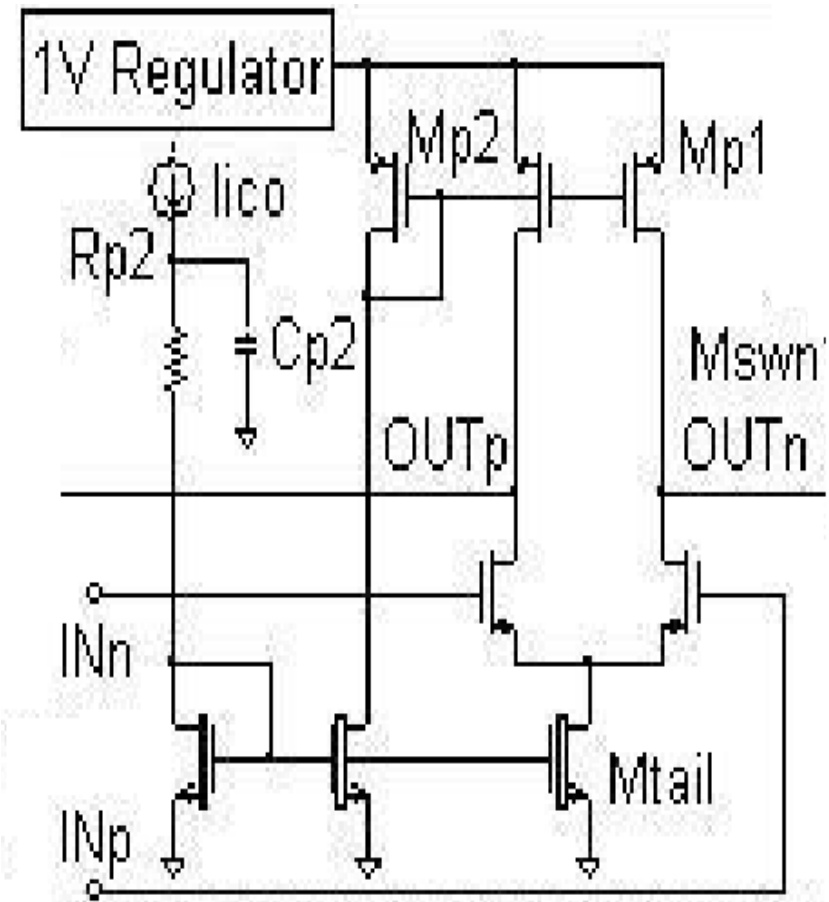
Reduce the Tail Current Noise



- Use a **single current leg to bias all the ring inverters** → provide a correlation between the noise of the individual inverter bias current → **first order cancellation** of the noise up to frequencies comparable with the inverter propagation time
- Add an RC filter to further reduce the noise of the bias current (help **only the thermal noise**)
- Use a high resistive degeneration in the bias current mirror (help **both thermal and 1/f noise**)

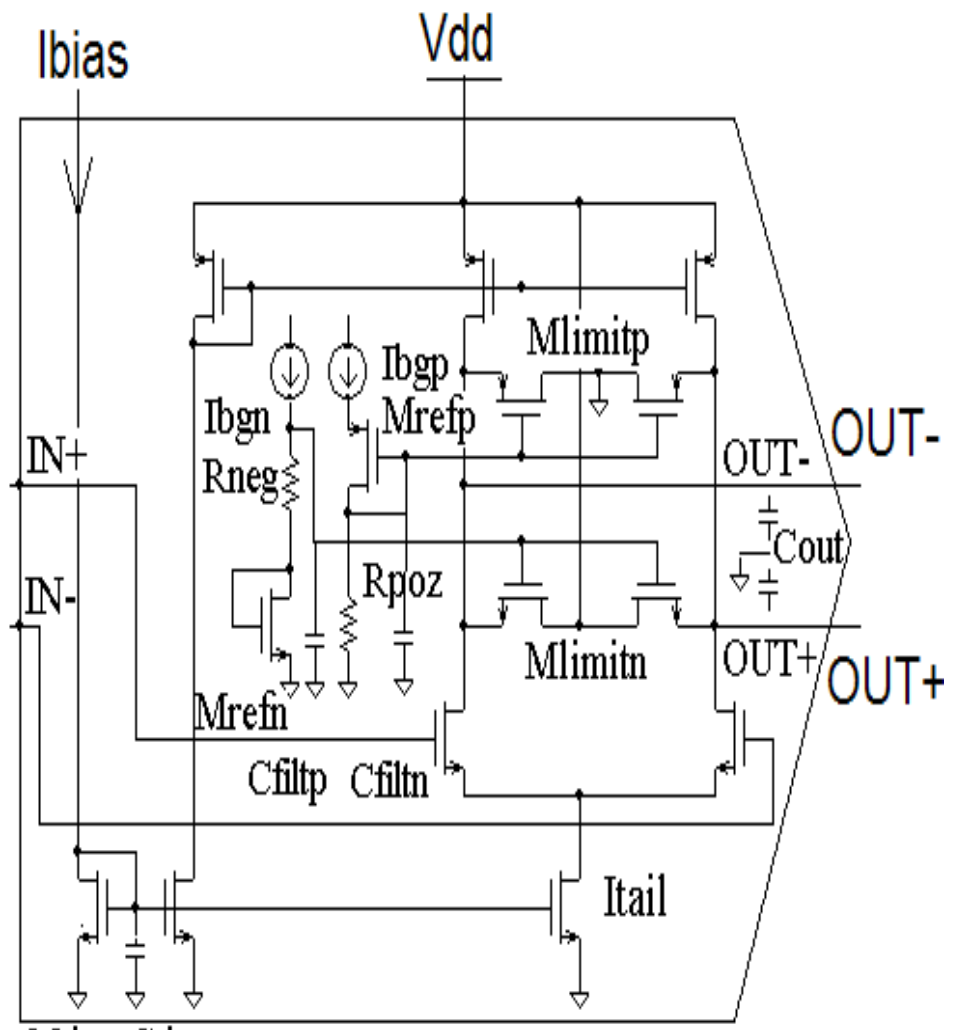
Saturated Load Differential Inverter

- Saturated load → **larger amplitude** of oscillation → reduces intrinsic phase noise
- Higher supply noise and spur injection → in the **unbalanced** condition when one of the load devices is in triode and the other one is OFF
- **NFET inverter**
 - Lower current → higher frequency
 - Larger $1/f$ noise
- **PFET inverter**
 - Lower $1/f$ noise
 - Higher bias current for given frequency



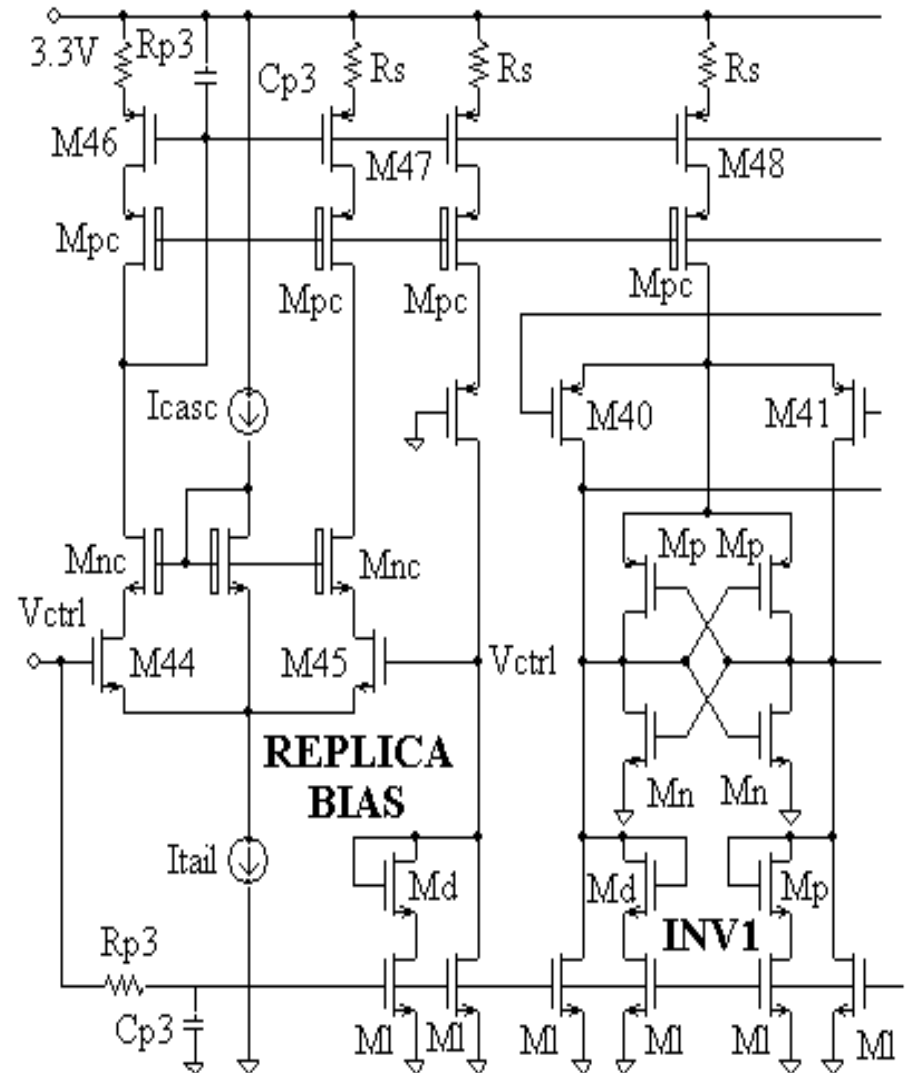
Clamped Amplitude Saturated Load

- To avoid strong supply noise and spurs injection the output **amplitude can be clamped** both in the positive and negative direction → **avoid going in triode** of both amplifier and load devices
- **Reduces slightly the amplitude** → limited intrinsic phase noise degradation



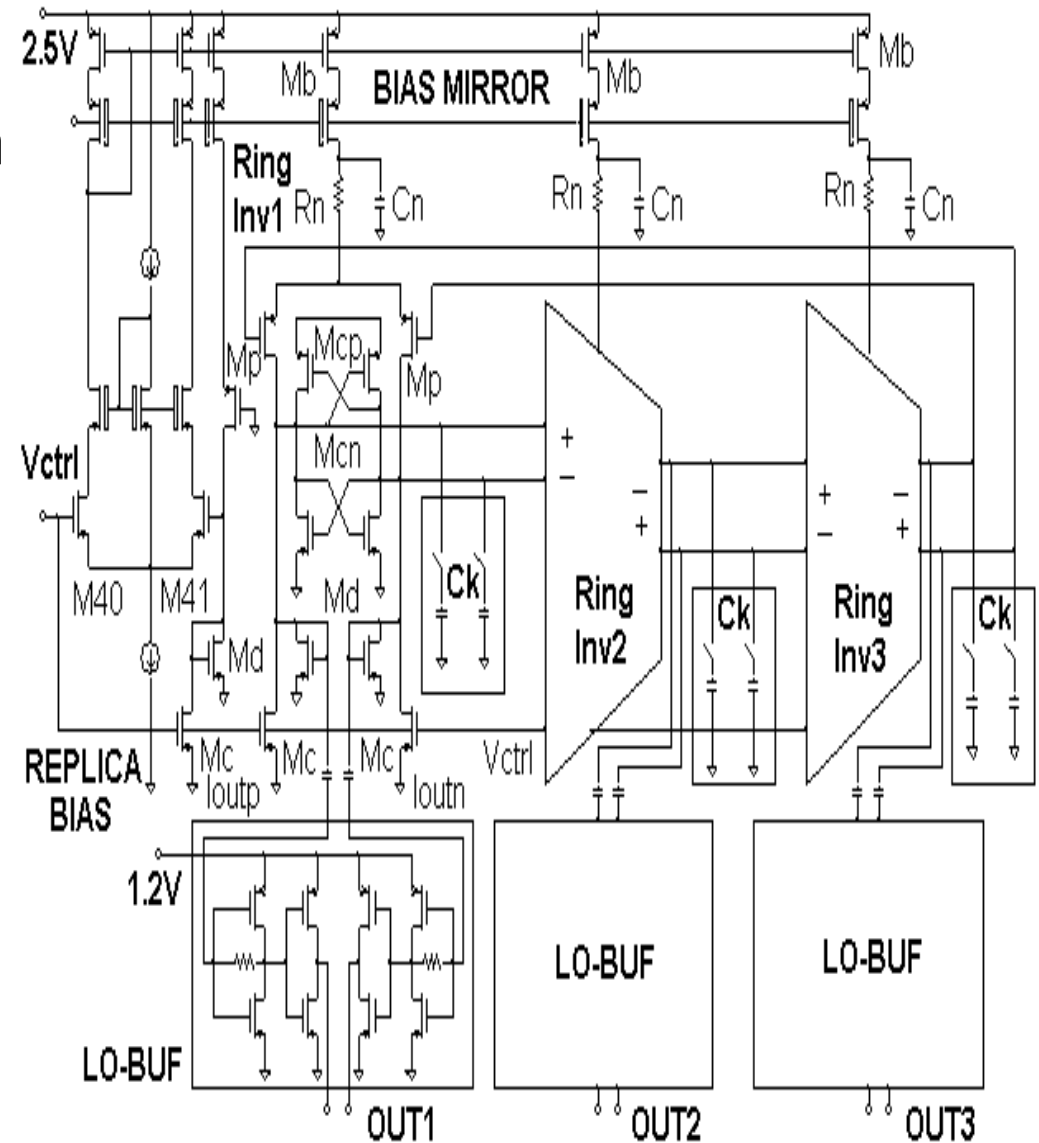
Triode Mode Differential Inverter

- Voltage controlled resistor load implemented with MOSFETs in triode region
- **Balanced load** → improve the supply rejection
- **Smaller amplitude** → allows higher oscillating frequency
- Replica bias leg generate a tail current that keeps the amplitude constant
- Triode load FTEs do not have $1/f$ noise while PFET amplifier has low $1/f$ noise



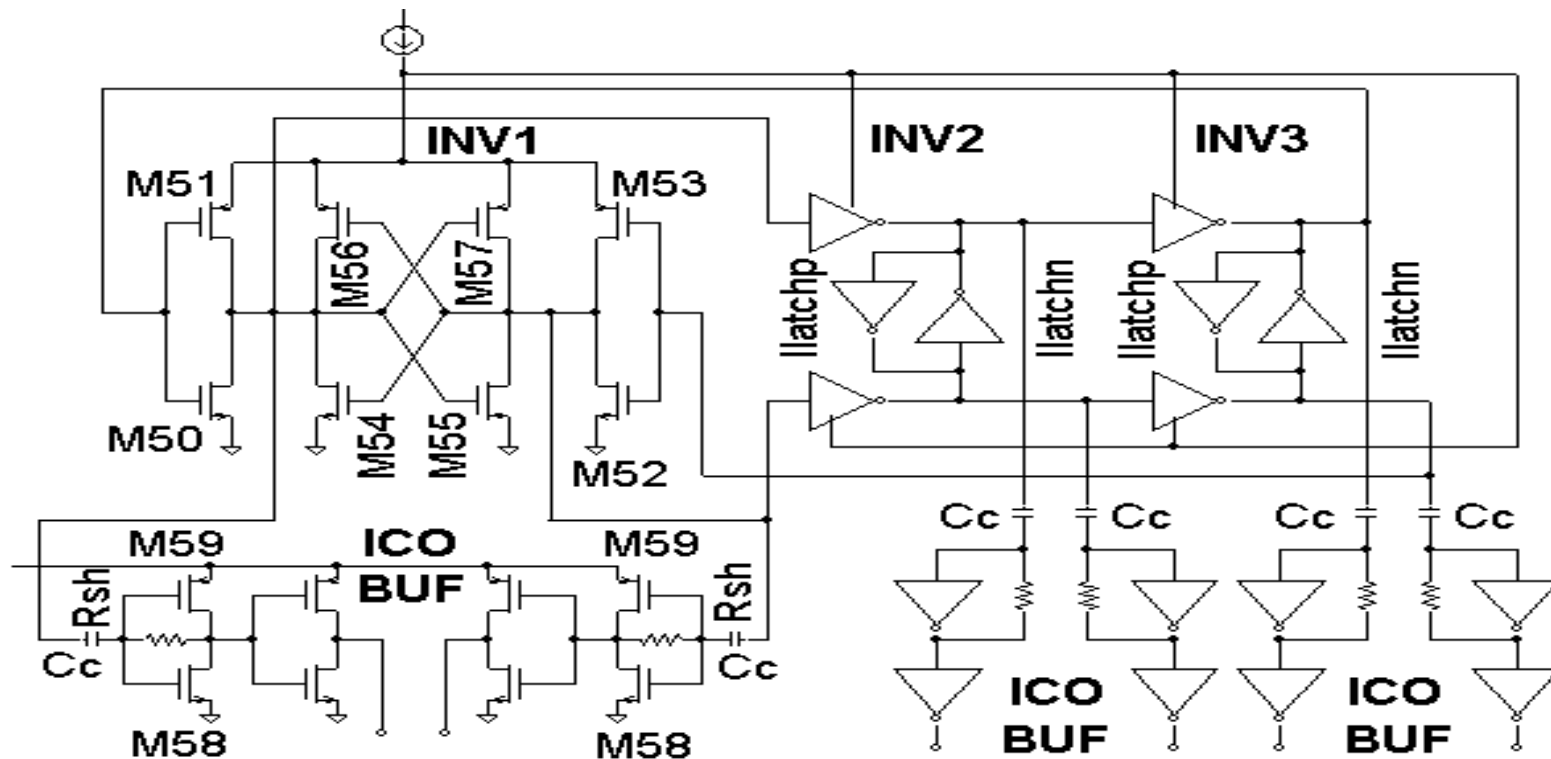
Reduced 1/f Noise Up-Conversion

- To reduce 1/f noise up-conversion the waveform need to be as symmetric as possible
- Use a **weak positive feedback NFET and PFET latch** to balance the waveform rise/fall times
- However the supplementary gate capacitance load from the latch stage reduces the maximum oscillating frequency



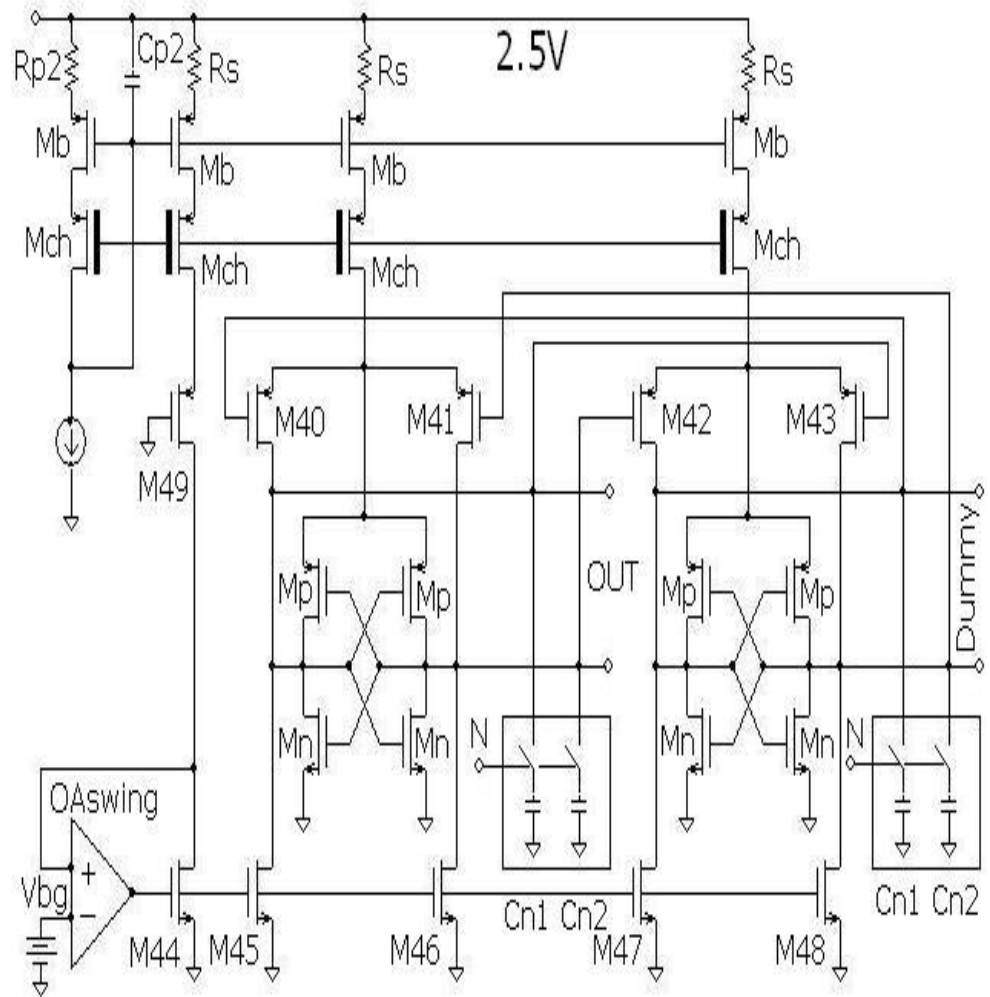
Pseudo-Differential Inverter Ring

- **Two single-ended inverter rings are coupled** with weak gain inverter latches → ensure a tight synchronism between the positive and negative clock paths
- High symmetry of the waveform → reduce the $1/f$ noise up-conversion



Two Stage Ring Oscillator

- Two inverters may **not have enough phase shift** to ensure a stable oscillation
- **Additional phase shift** can be provide by:
 - **Inductive peaking** (either real inductor or active simulated inductor)
 - **Local positive feedback** loops using cross-coupled latch stages
- Two stage ring oscillators offer the highest oscillating frequency and the lowest phase noise



VCO Clock-Buffer Requirements

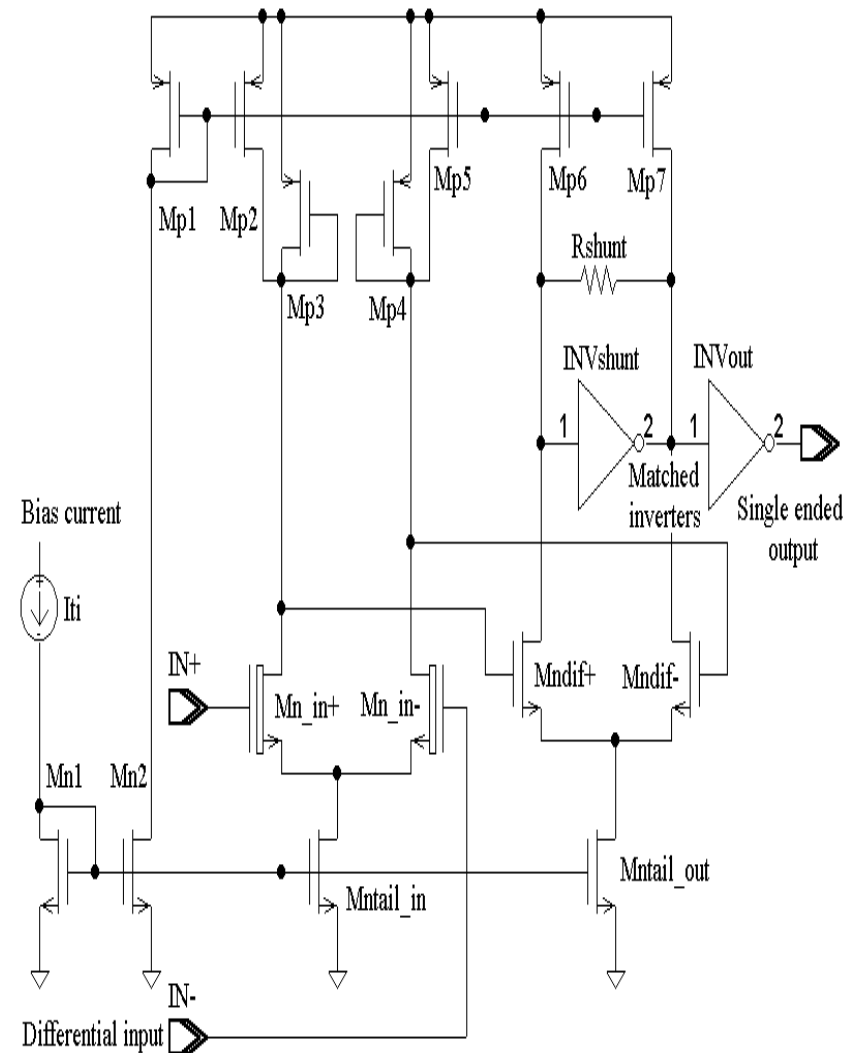
- Most applications require a **50% duty cycle**
- Present a **low capacitive load** to the oscillator (prefer a constant capacitance rather than $C(V)$)
- Ensure a **symmetric loading** to all the ring inverters
- **Square-up** the sine/triangular waveform provided by the VCO (hard to get large gains at multi-GHz frequencies)
- Avoid coupling supply noise and spurs → VCO-BUF uses the **same regulated supply as the VCO** - the impulsive supply current of the buffer does not impact VCO phase noise as it is in perfect synchronism with the generated clock
- **Second order distortions** resulted from the asymmetry (e.g. VT mismatch) can degrade oscillator's phase noise

50% Duty Cycle Clock

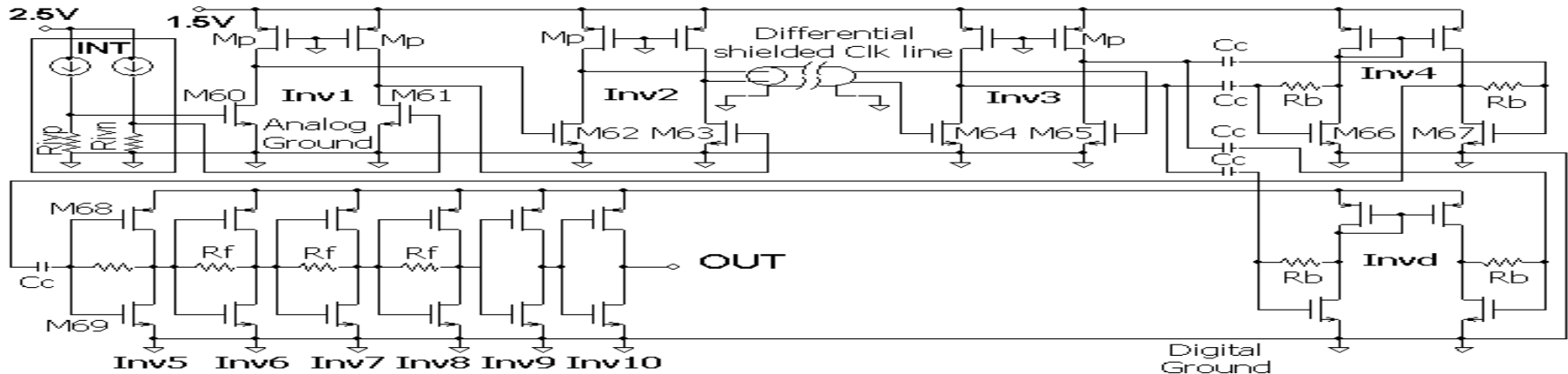
- At lower frequencies the established way of ensuring a 50% duty cycle is to **run the oscillator at twice** the required output **frequency** and than **divide by 2**
 - ↓ **power hungry** solution → the VCO runs at twice the frequency
 - ↓ not applicable to 5-10GHz PLLs due to the limited gain-bandwidth of the CMOS inverters
- Dividing down the VCO output clock also ensures **quadrature outputs** - required by most communication systems

Dual Shunt-Feedback 50% Duty Cycle VCO-Buffer

- Use a differential pair with **dual shunt feedback**:
 - **Resistor feedback** → restricts the output swing around the trip point of the 2nd inverter
 - **Inverter feedback** → matches the trip point of the first two stages in the VCO-BUF, ensuring a precise 50% duty cycle over process and temp.

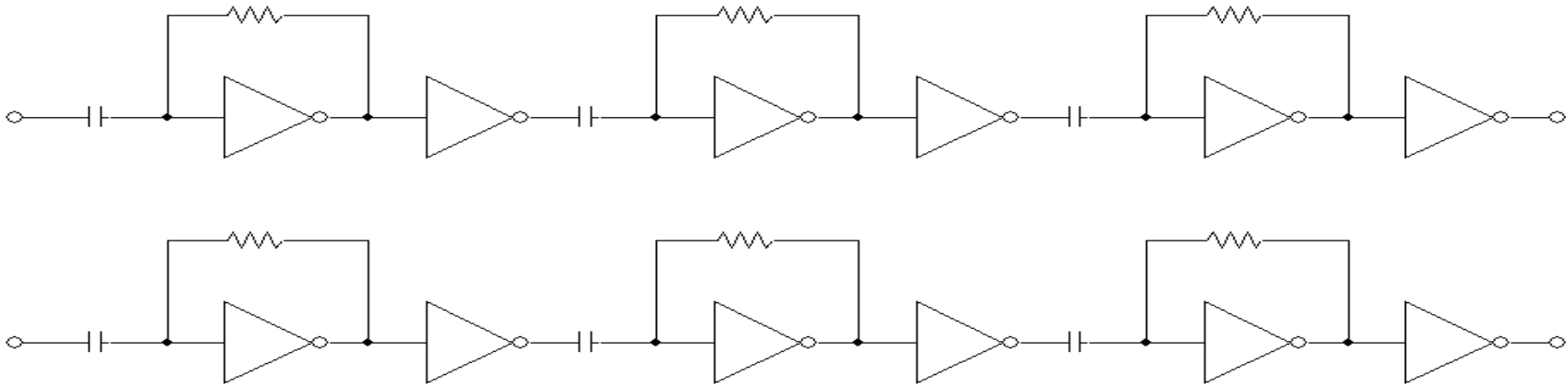


Mixed NMOS-CMOS 50% Duty Cycle VCO-Buffer



- **CMOS inverters** have a large input capacitance → prefer **NMOS inverters** which are faster and present a lower input capacitance (but have less drive capability)
- The front-end is built with pseudo-differential NMOS stages → ensure fast edges
- Back-end is CMOS → large drive capability
- Cascaded resistive shunt feedback stages ensure the 50% duty cycle

Pseudo-Differential Buffer



- The highest bandwidth in a given process is achieved by **single ended inverter** stages
- Use **two single ended signal paths** to achieve a pseudo-differential clock path
- AC coupling is used to avoid pulse width distortion
- Use C_c after each 2 inverters to avoid large offset voltage accumulation
- First two stages of equal size to square-up the waveform and then scale-up the size for drive capability

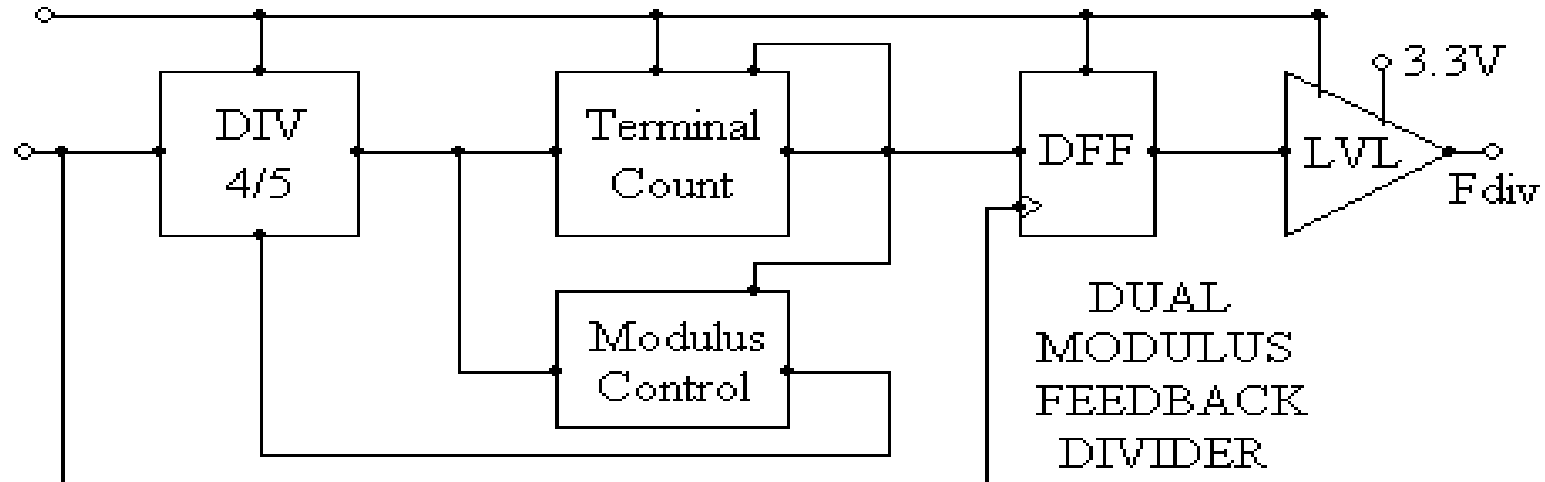
High-frequency Divider Requirements

- Ensure **multi-GHz operation**
- Avoid large supply currents (need a **high reverse PSRR shunt regulator** to isolate the impulsive supply current from the global PLL supply)
- Digital design styles:
 - Standard CMOS → usually not enough fast
 - CML CMOS logic → fastest, but need large DC current
 - Dynamic CMOS logic → fast operation and no DC current

Divider Phase Noise / Jitter

- The different clock paths within the divider can add significant amount of phase noise/jitter
- To minimize divider jitter the output divided-down clock is **re-synchronized** either at the full VCO rate (if possible) or at a lower rate ($f_0/2$, $f_0/4$)
- By re-synchronizing all jitter introduced by the divider is eliminated → jitter limited by the **last re-synchronization DFF and its clock buffer**

Dual Modulus Divider Architecture



- The pre-scalar has a controlled division modulus (2/3, 4/5, 8/9, etc.)
- The higher the front-end division factor → lower the frequency requirements for the back-end dividers
- Back-end modulus control divider determines the $N/N+1$ division of the front-end
- Back-end terminal count divider generates the output clock and resets the entire divider

CONCLUSIONS

- Selecting the **architecture** for the PLL building blocks is key for achieving high performance multi-GHz frequency synthesizers
- **XTAL oscillators** → move from the widely used Pierce configuration to the lower phase noise all PFET common drain Colpitts architecture
- **REF-BUF** dominates the phase noise in wideband PLLs → current starved inverters offer a significantly lower noise and supply spurs sensitivity
- **PFD** need to have a fast reset propagation time and also fast rise/fall times → migrate from standard CMOS 7 NAND architecture to dynamic D-flip-flop configurations
- **Charge-pumps** need to have a fast switching and accurately matched currents and switching times → current steering is the architecture of choice with dynamic matching DC loop and charge sharing and clock-feedthrough cancellation

CONCLUSIONS - Continued

- **Loop filters** need to add negligible noise and have a very high PSRR. Reference spurs are a big concern in many communication applications → migrate from continuous time filters to hybrid and fully sampled filters that completely isolate the oscillator from the charge-pump switching action and spread the impulsive control energy over an entire reference clock cycle. Digital filtering further reduces the loop filter noise contribution
- **LC Oscillators** → migrate from current-mode towards voltage-mode architectures that provide a significantly lower $1/f$ noise up-conversion. Use bondwires for the tuned tank and a high resolution calibration network to reduce the oscillator gain → help both spurs and phase noise
- **Ring Oscillators** → Differential inverters are preferred in large mixed signal ICs due to their higher supply and substrate noise immunity. Minimize the number of inverters in the ring brings both a high frequency capability and a lower phase noise. Ensure a symmetric waveform for lower $1/f$ noise up-conversion and minimize the tail current noise

CONCLUSIONS - Continued

- **Multi-GHz clock buffers** → use the simplest gain stages available for maximum gain-bandwidth. Pseudo-differential inverter chains with AC coupling for pulse-width distortion cancellation became a standard procedure
- **Multi-GHz dividers** → dual modulus architectures became standard, having a high frequency front-end prescaler built with CML or dynamic CMOS logic and a low frequency back-end built with standard CMOS or dynamic logic
- **Power supply partitioning and regulation** is an important part of the synthesizer design → to ensure low supply injected spurs use several series and shunt regulators together with passive and active RC filtering